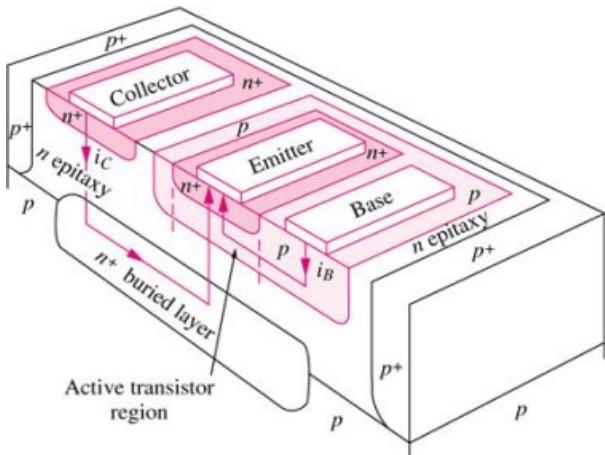
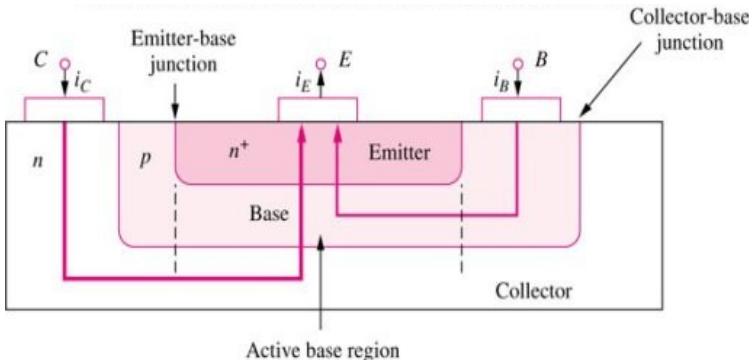


# Bipolar Junction Transistors

# Introduction

- Bipolar transistors are one of the main ‘building-blocks’ in electronic systems
- They are used in both analogue and digital circuits
- As an amplifier in analogue electronics and as a switch in computer
- They incorporate two *pn* junctions and are sometimes known as **bipolar junction transistors** or **BJTs**
- Here will refer to them simply as **bipolar transistors**

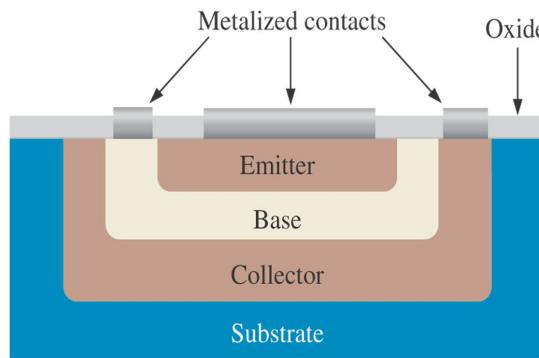
# Physical Structure



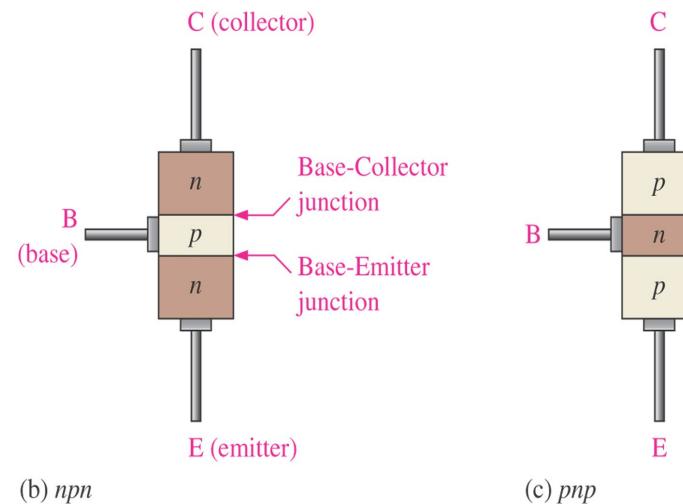
- The BJT consists of 3 alternating layers of *n*- and *p*-type semiconductor called **emitter (E)**, **base (B)** and **collector (C)**.
- The majority of current enters collector, crosses the base region and exits through the emitter. A small current also enters the base terminal, crosses the base-emitter junction and exits through the emitter.
- Carrier transport in the active base region directly beneath the heavily doped (*n<sup>+</sup>*) emitter dominates the *i-v* characteristics of the BJT.

# Architecture of BJTs

- The bipolar junction transistor (BJT) is constructed with three doped semiconductor regions separated by two *pn* junctions
- Regions are called **emitter**, **base** and **collector**



(a) Basic epitaxial planar structure

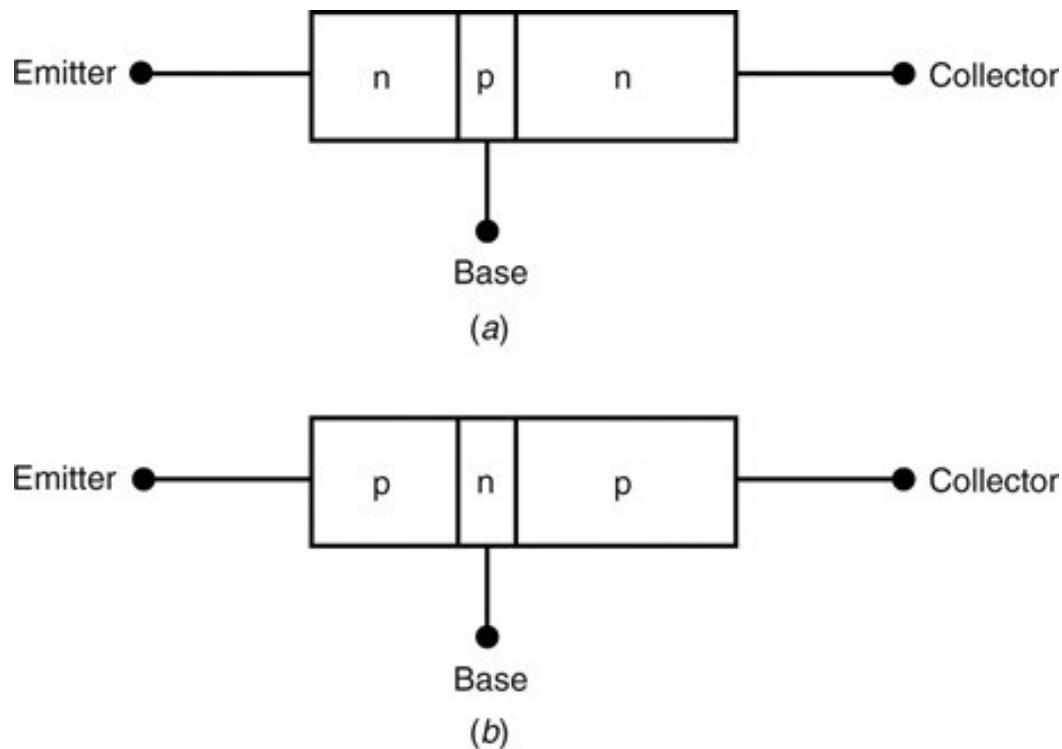


(b) *npn*

(c) *pnp*

# Architecture of BJTs

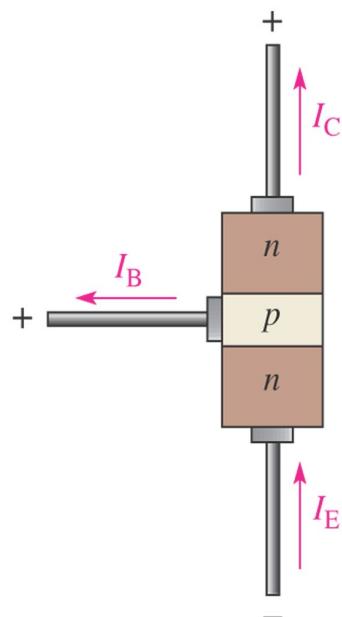
- The emitter region is heavily doped and its job is to emit carriers into the base.
- The base region is very thin and lightly doped.
- Most of the current carriers injected into the base from emitter pass on to the collector.
- The collector region is moderately doped and is the largest of all three regions.



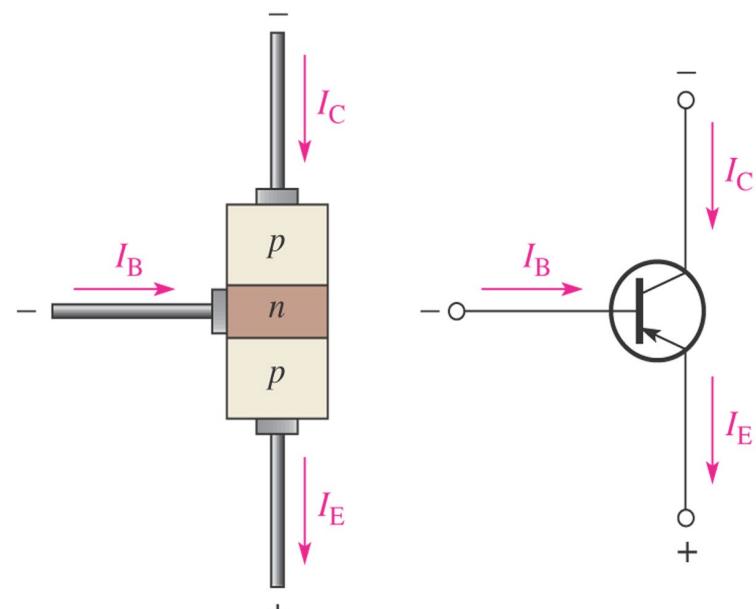
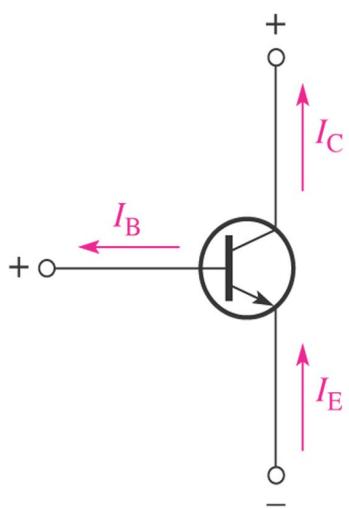
# Architecture of BJTs

- There are two types of BJTs, the *npn* and *pnp*
- The two junctions are termed the *base-emitter* junction and the *base-collector* junction
- The term bipolar refers to the use of both holes and electrons as charge carriers in the transistor structure
- In order for the transistor to operate properly, the two junctions must have the correct dc bias voltages
  - the base-emitter (BE) junction is forward biased( $>=0.7V$  for Si,  $>=0.3V$  for Ge)
  - the base-collector (BC) junction is reverse biased

**FIGURE** Transistor symbols.

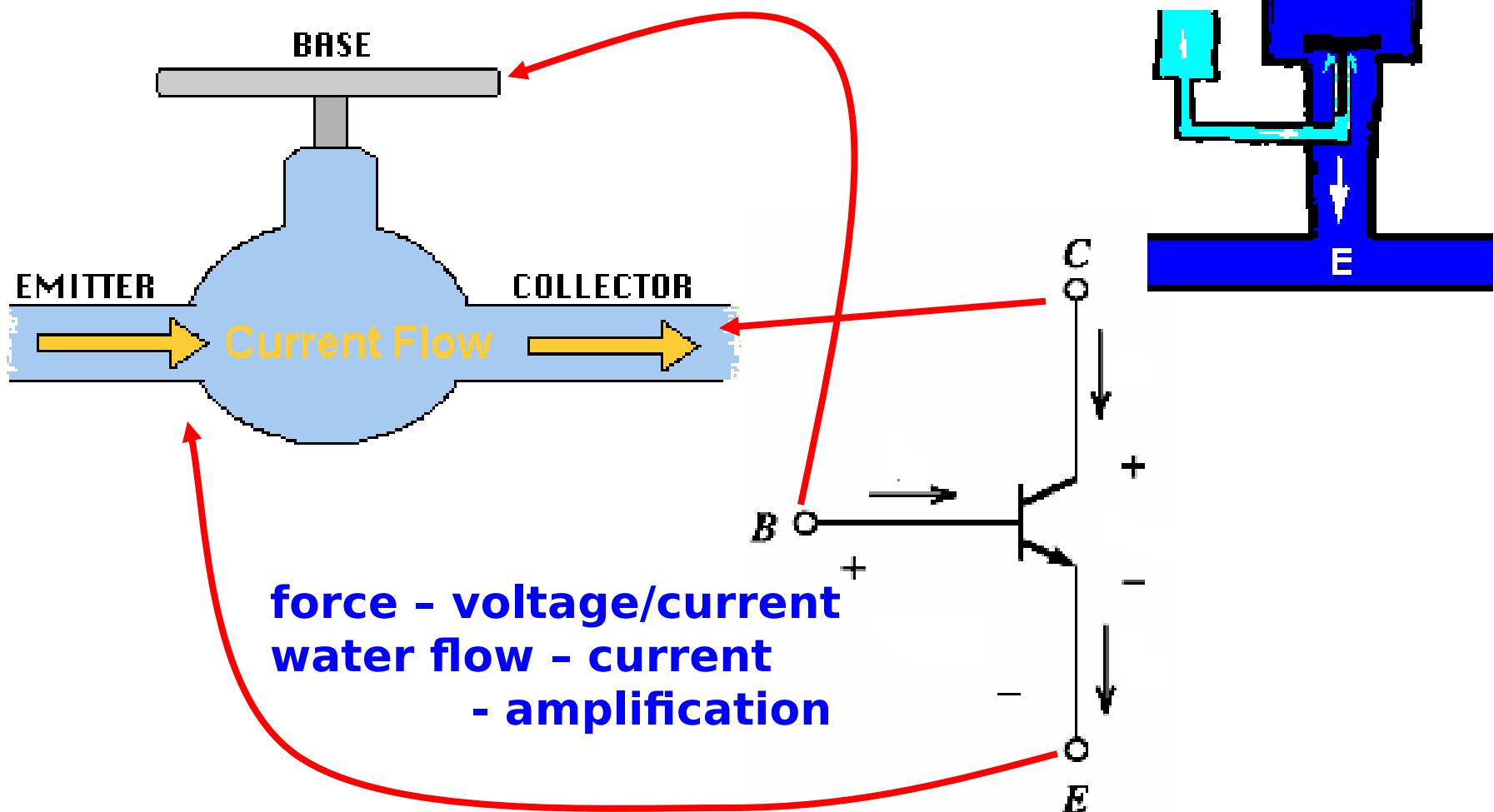


(a) *npn*



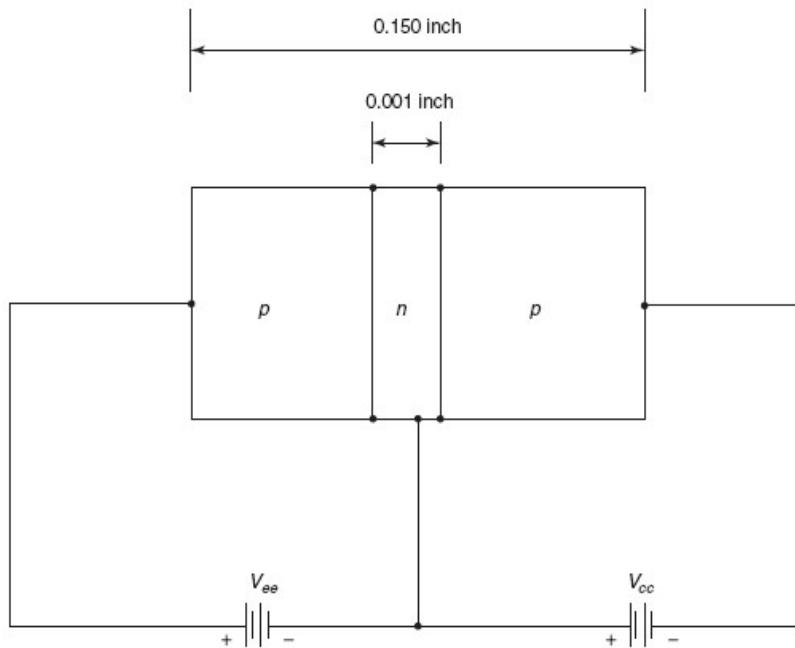
(b) *pnp*

# Understanding of BJT

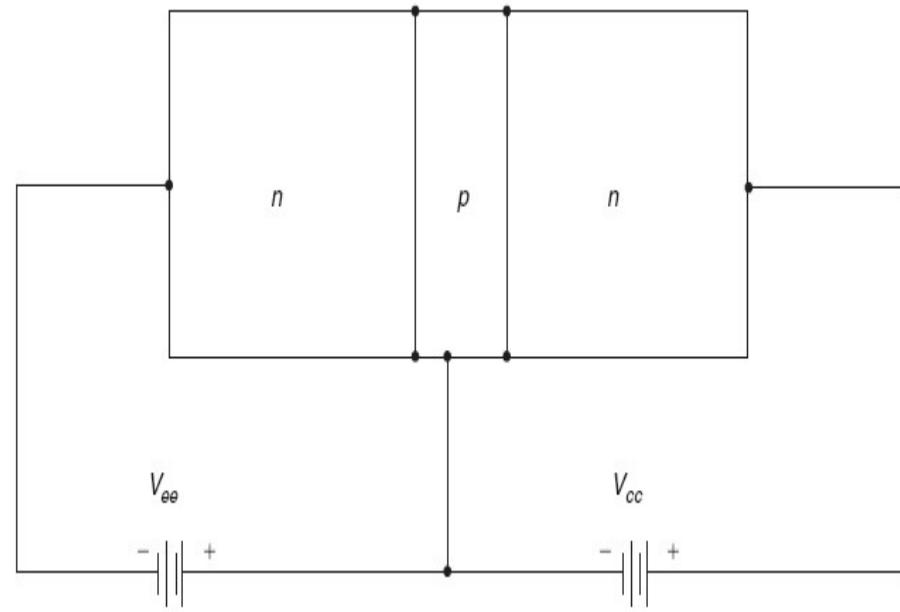


# FORMATION OF p–n–p AND n–p–n JUNCTIONS

- ❖ When an *n-type thin semiconductor layer is placed between two p-type semiconductors, the resulting structure is known as the p–n–p transistor.*
- ❖ When a *p-type semiconductor is placed between two n-type semiconductors, the device is known as the n–p–n transistor.*



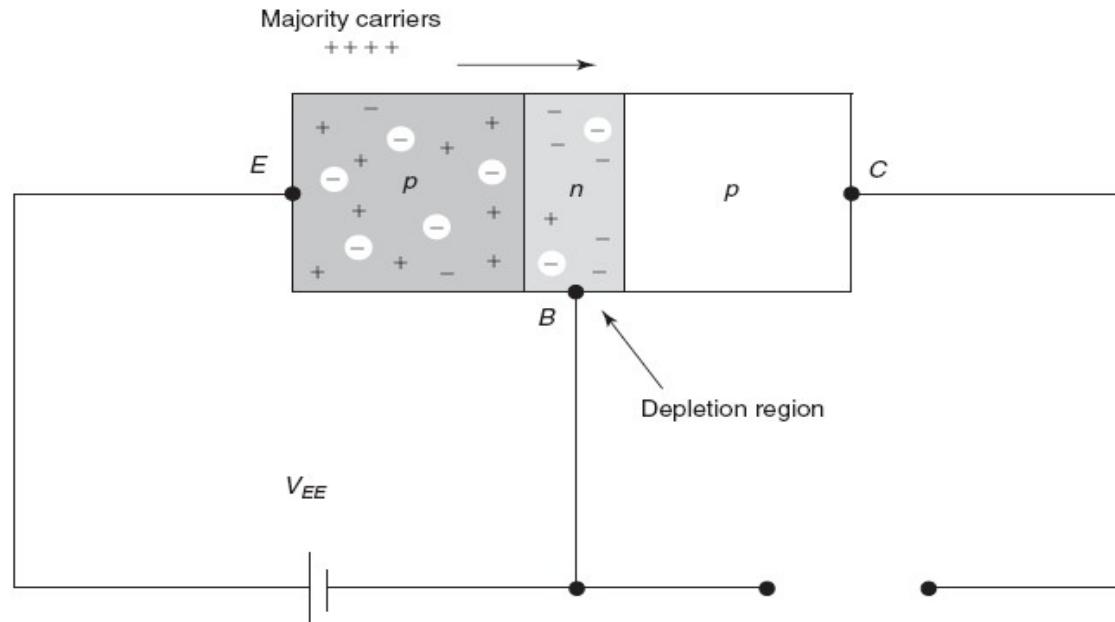
*p–n–p transistor*



*n–p–n transistor*

# TRANSISTOR MECHANISM

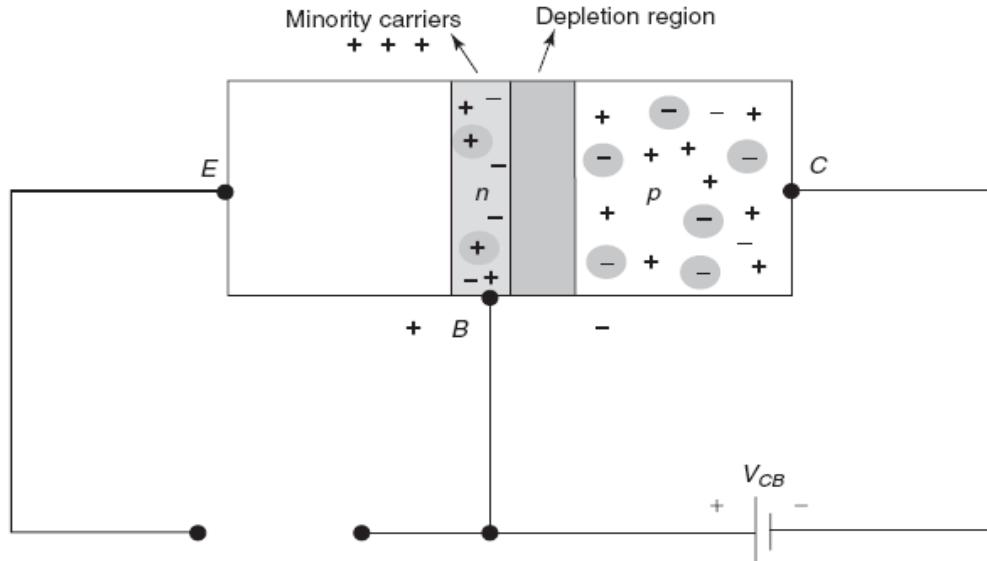
- ❖ The basic operation of the transistor is described using the *p–n–p transistor*.
- ❖ *The p–n junction of the transistor is forward-biased whereas the base-to-collector is without a bias.*
- ❖ The depletion region gets reduced in width due to the applied bias, resulting in a heavy flow of majority carriers from the *p-type to the n-type material gushing down the depletion region and reaching the base*.
- ❖ The forward-bias on the emitter–base junction will cause current to flow.



Forward-biased junction of a *p–n–p transistor*

# TRANSISTOR MECHANISM

- ❖ For easy analysis, let us now remove the base-to-emitter bias of the *p–n–p transistor*.
- ❖ The flow of majority carriers is zero, resulting in a minority-carrier flow. Thus, one *p–n junction of a transistor* is reverse-biased, while the other is kept open.
- ❖ The operation of this device becomes much easier when they are considered as separate blocks. In this discussion, the drift currents due to thermally generated minority carriers have been neglected, since they are very small.



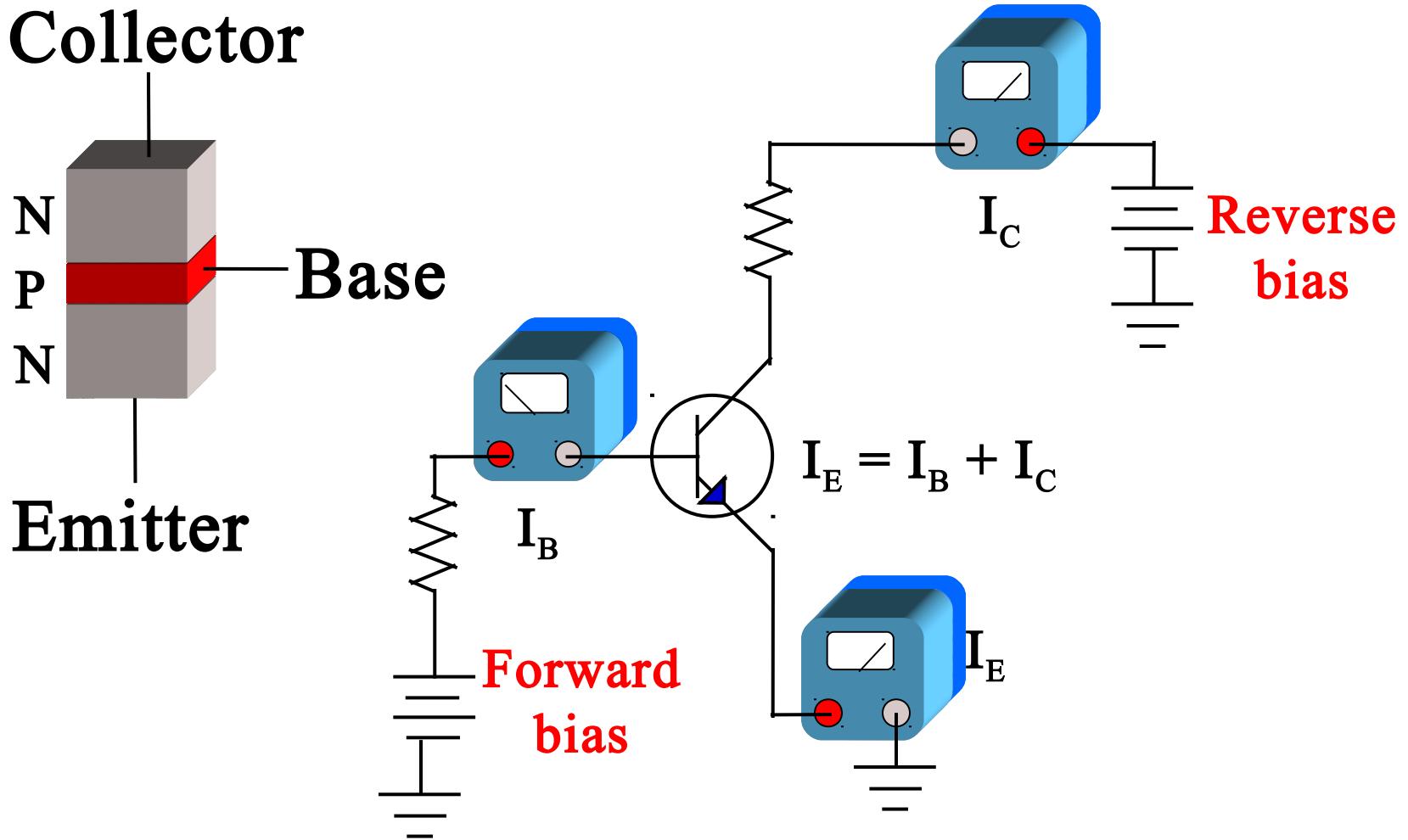
Reverse-biased junction of a *p–n–p transistor*

# Proper Transistor Biasing

---

- For a transistor to function properly as an amplifier, the **emitter-base** junction must be forward-biased and the **collector-base** junction must be reverse-biased.
  - The common connection for the voltage sources are at the base lead of the transistor.
  - The emitter-base supply voltage is designated  $V_{EE}$  and the collector-base supply voltage is designated  $V_{CC}$ .
  - For silicon, the barrier potential for both EB and CB junctions equals 0.7 V
-

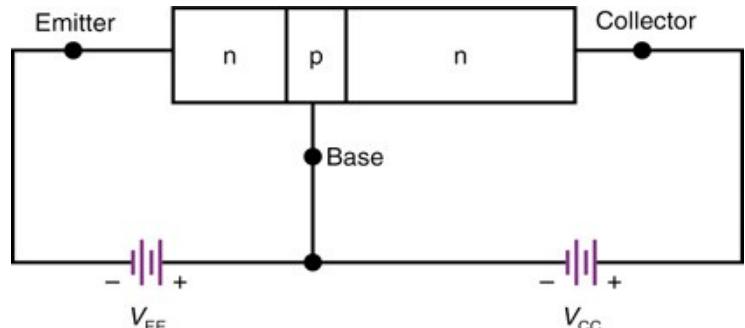
# Transistor Biasing



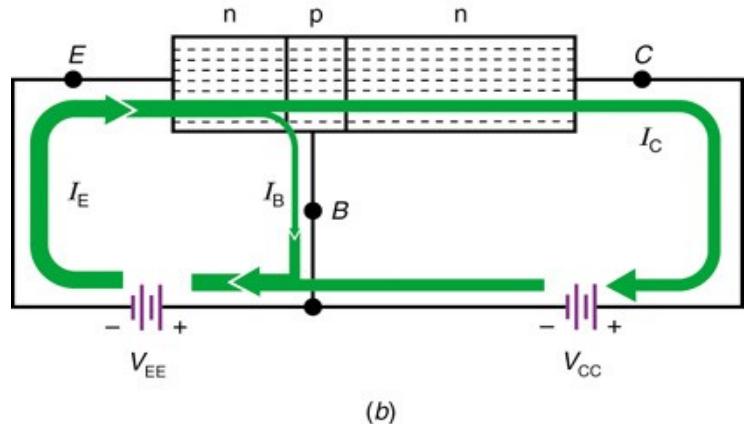
# Proper Transistor Biasing

---

- Fig. shows transistor biasing for the *common-base* connection.
- Proper biasing for an npn transistor is shown in (a).
- The EB junction is forward-biased by the emitter supply voltage,  $V_{EE}$ .
- $V_{CC}$  reverse-biases the CB junction.
- Fig. (b) illustrates currents in a transistor.
- CE voltage of an npn transistor must be positive
- Ratio of  $I_C$  to  $I_E$  is called DC alpha  $\alpha_{dc}$



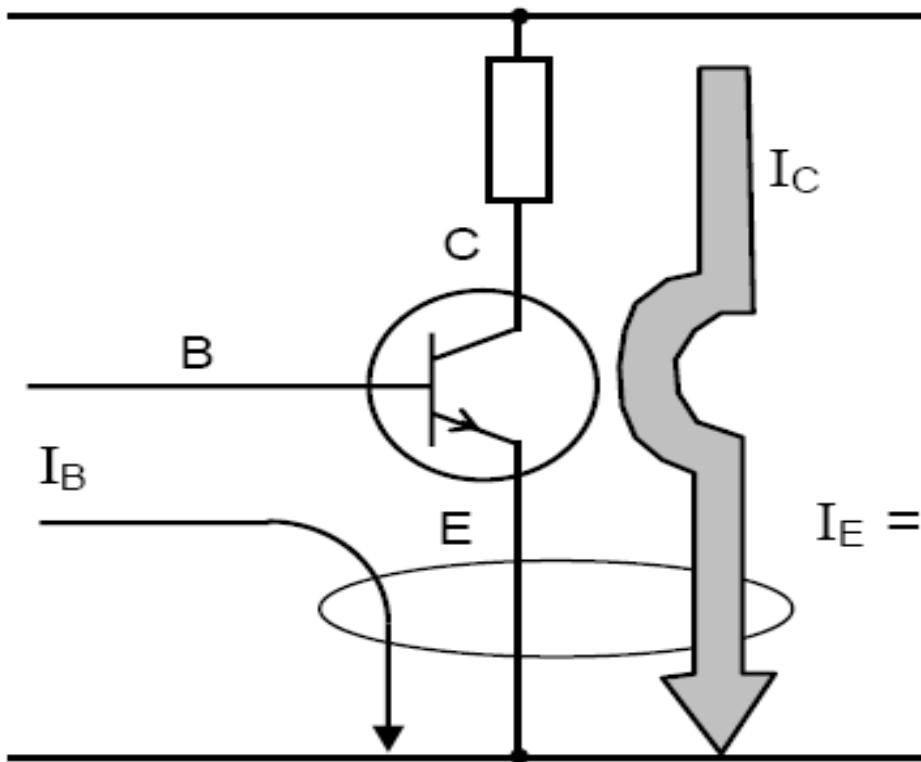
(a)



(b)

# Emitter, collector and base currents

---



$$(\text{emitter current}) = (\text{base current}) + (\text{collector current})$$

$$I_E = I_B + I_C$$

$$I_E = I_C + I_B$$

# Transistor Configurations

- common emitter (CE)
- common base (CB)
- common collector (CC).

## Circuit Configuration

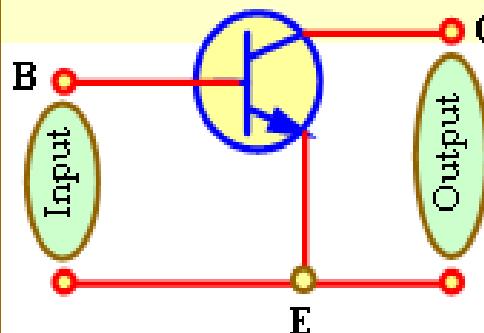


Figure 5a C-E Circuit

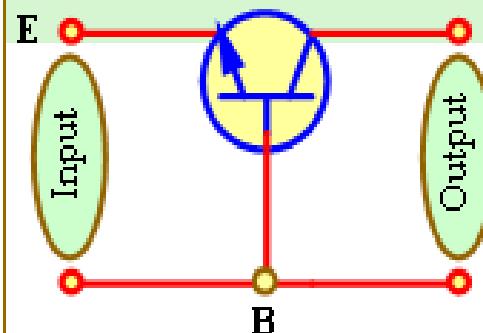


Figure 5b C-B Circuit

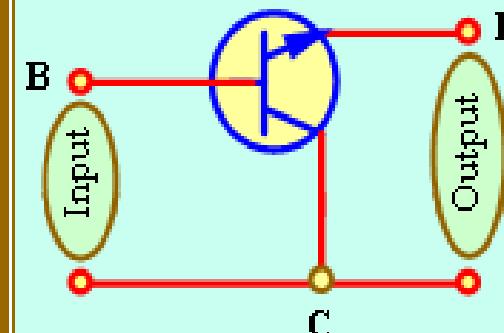
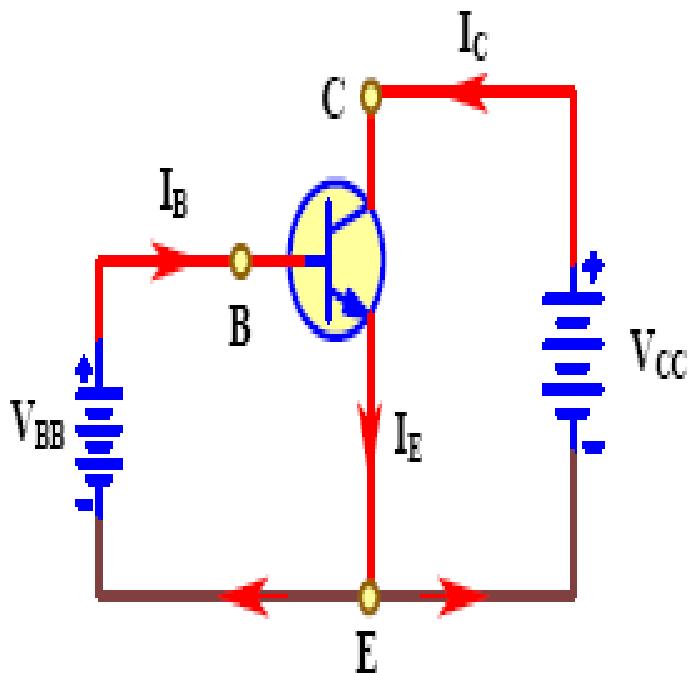


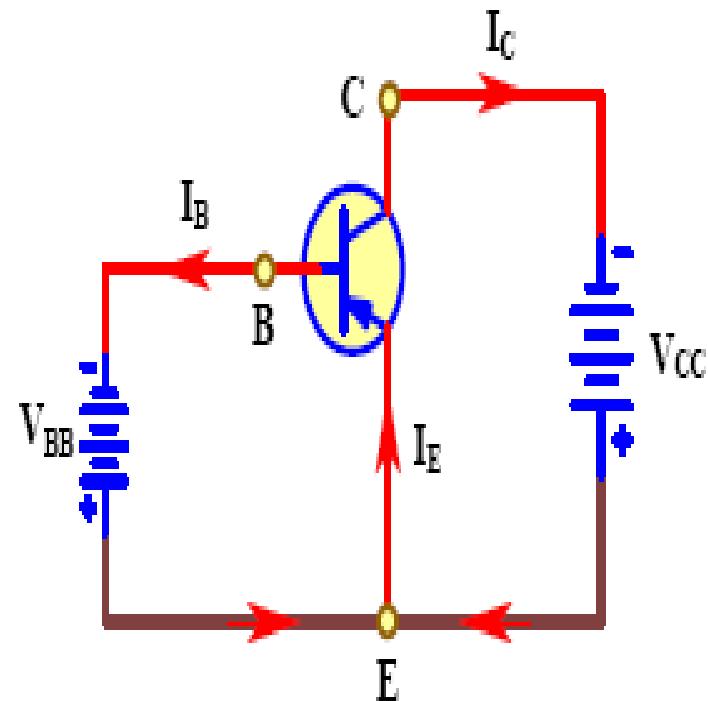
Figure 5c C-C Circuit

Current Gain	Medium (50)	Low (0.99)	Highest (60)
Voltage Gain	High (100 to 500)	Highest (200 to 2000)	Low (less than 1)
Power Gain	Highest (200 to 20,000)	Medium (200 to 1000)	Low (20 to 80)
$R_{IN}$	Medium ( $1k\Omega$ to $5k\Omega$ )	Very low ( $15\Omega$ to $150\Omega$ )	High ( $2k\Omega$ to $500k\Omega$ )
$R_{OUT}$	High ( $40\Omega$ to $60k\Omega$ )	Very high ( $250k\Omega$ to $1M\Omega$ )	Very low ( $25\Omega$ to $1k\Omega$ )
Phase shift	$180^\circ$	$0^\circ$	$0^\circ$

# Currents in CE Circuit



(a) Currents in C-E (NPN) circuit



(b) Currents in C-E (PNP) circuit

# Operating Regions

- Since emitter lead is common, this connection is called common-emitter connection

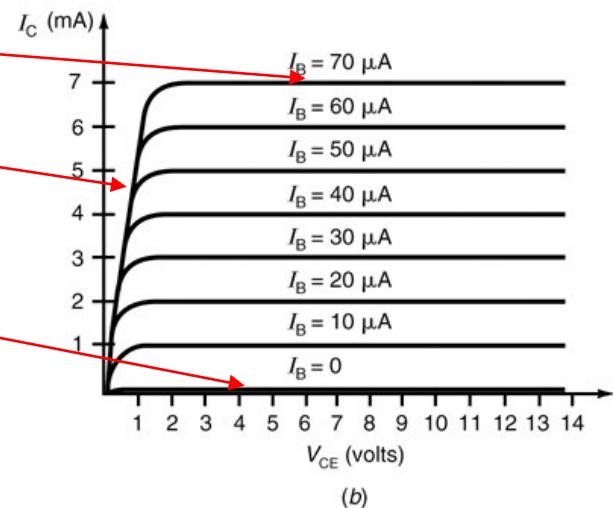
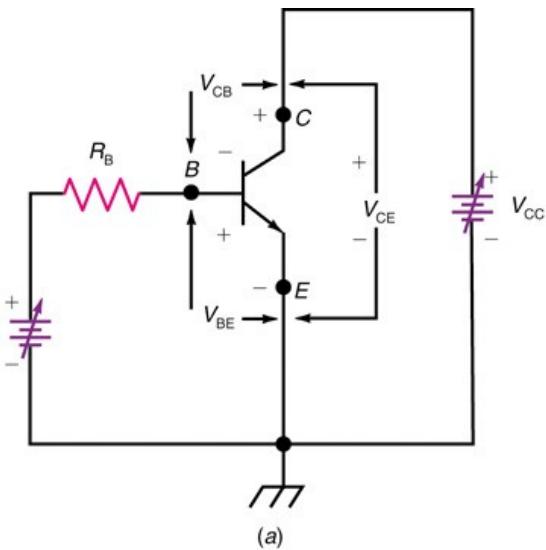
- Collector current  $I_C$  is controlled solely by the base current,  $I_B$ .

- By varying  $I_B$ , a transistor can be made to operate in any one of the following regions

- Active
- Saturation
- Breakdown
- Cutoff

- Ratio of  $I_C$  to  $I_B$  is called DC beta  $\beta_{dc}$

Fig. Common-emitter connection (a) circuit. (b) Graph of  $I_C$  versus  $V_{CE}$  for different base current values.



# BJT characteristics

- Current Gain:
  - $\alpha$  is the fraction of electrons that diffuse across the narrow Base region
  - $1 - \alpha$  is the fraction of electrons that recombine with holes in the Base region to create base current
- The current Gain is expressed in terms of the  **$\beta$  (beta)** of the transistor (often called  $h_{fe}$  by manufacturers).
- **$\beta$  (beta)** is Temperature and Voltage dependent.
- It can vary a lot among transistors (common values for signal BJT: 20 - 200).

$$I_C = \alpha I_E$$

$$I_B = (1 - \alpha) I_E$$

$$\beta = \frac{I_C}{I_B} = \frac{\alpha}{1 - \alpha}$$

# Transistor Currents

- $I_E = I_B + I_C$

- $I_C = I_E - I_B$

$$I_B = I_E - I_C$$

- $\beta_{dc} = \frac{I_C}{I_B}$

$$\beta_{dc} = \frac{\alpha_{dc}}{1 - \alpha_{dc}}$$

- $\alpha_{dc} = \frac{I_C}{I_E}$

- $\alpha_{dc} = \frac{\beta_{dc}}{1 + \beta_{dc}}$

# Operating Regions

- Active Region
  - Collector curves are nearly horizontal
  - $I_C$  is greater than  $I_B$  ( $I_C = \beta_{dc} \times I_B$ )
- Saturation
  - $I_C$  is not controlled by  $I_B$
  - Vertical portion of the curve near the origin
- Breakdown
  - Collector-base voltage is too large and collector-base diode breaks down
  - Undesired collector current
- Cutoff
  - $I_B = 0$
  - Small collector current flows  $I_C \approx 0$

# Example

- A transistor has the following currents:

$$I_E = 15 \text{ mA}$$

$$I_B = 60 \mu\text{A}$$

Calculate  $\alpha_{dc}$ , and  $\beta_{dc}$

- $I_C = I_E - I_B = 14.94 \text{ mA}$

- $\alpha_{dc} = 0.996$

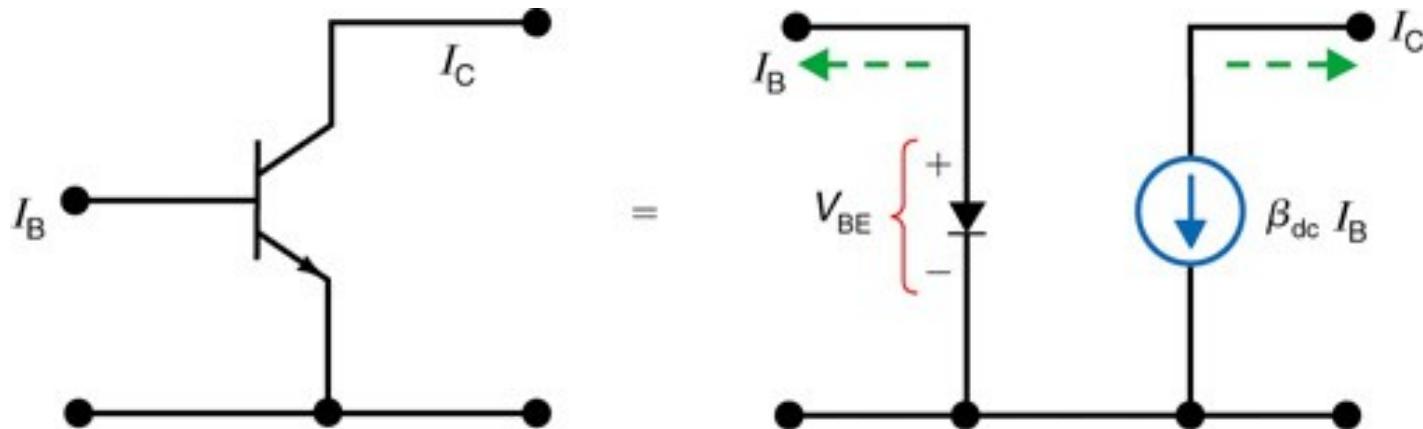
- $\beta_{dc} = 249$

# Transistor Operation Regions

Operation Region	Bias	Application
CUT OFF REGION	$I_B$ and $I_c$ are 0 (base-emitter junction is reverse biased)	Open Switch (OFF)
SATURATION REGION	Base emitter junction is forward biased; $I_B$ flows	Closed Switch (ON)
ACTIVE REGION	B-E junction is forward biased but C-E junction is reverse biased;	Amplifier

# Operating Regions

- Fig. shows the **dc equivalent** circuit of a transistor operating in the active region.
- The base-emitter junction acts like a forward-biased diode with current,  $I_B$ .
- Usually, the second approximation of a diode is used.
- If the transistor is silicon, assume that  $V_{BE}$  equals 0.7 V.



# Transistor can act as a Switch

## A switching circuit

### i) Transistor as an OFF switch

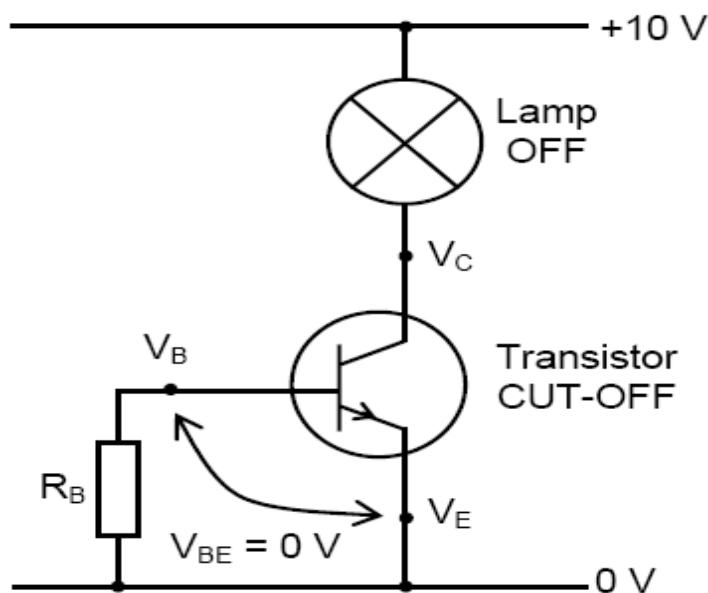


Fig. 5.25(a) – Transistor in CUT-OFF Condition (no current)

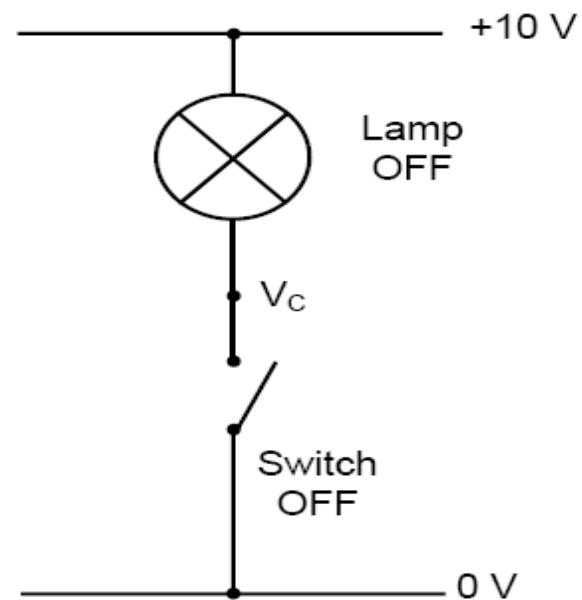


Fig. 5.25(b) – Transistor compared to switch

ii) Transistor as an ON switch

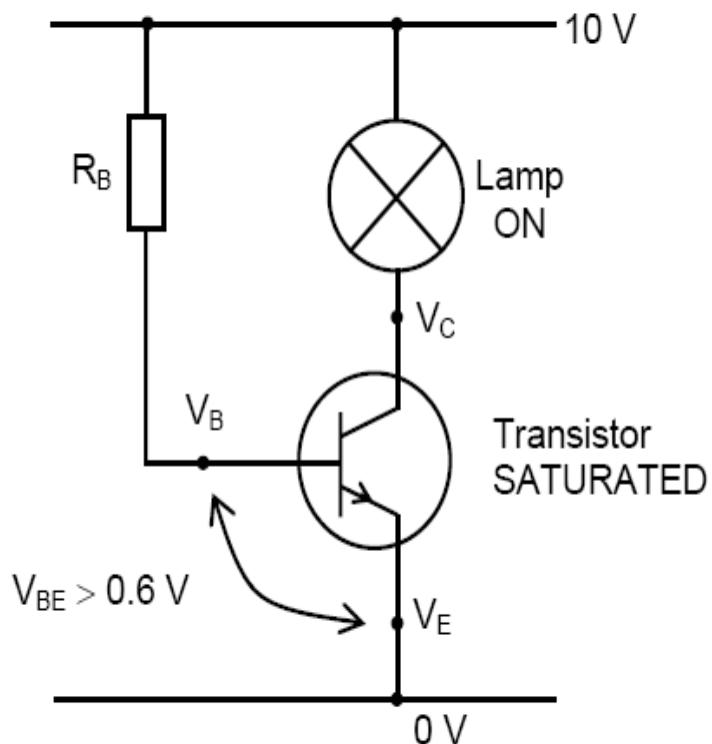


Fig. 5.26(a) – Transistor in SATURATED Condition (maximum current)

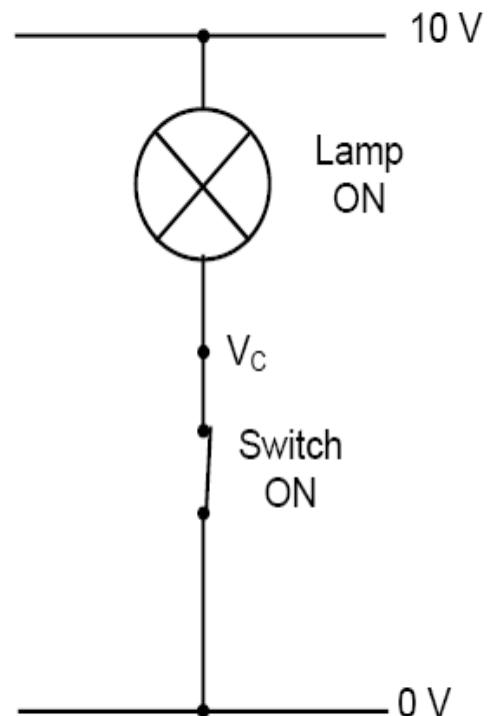
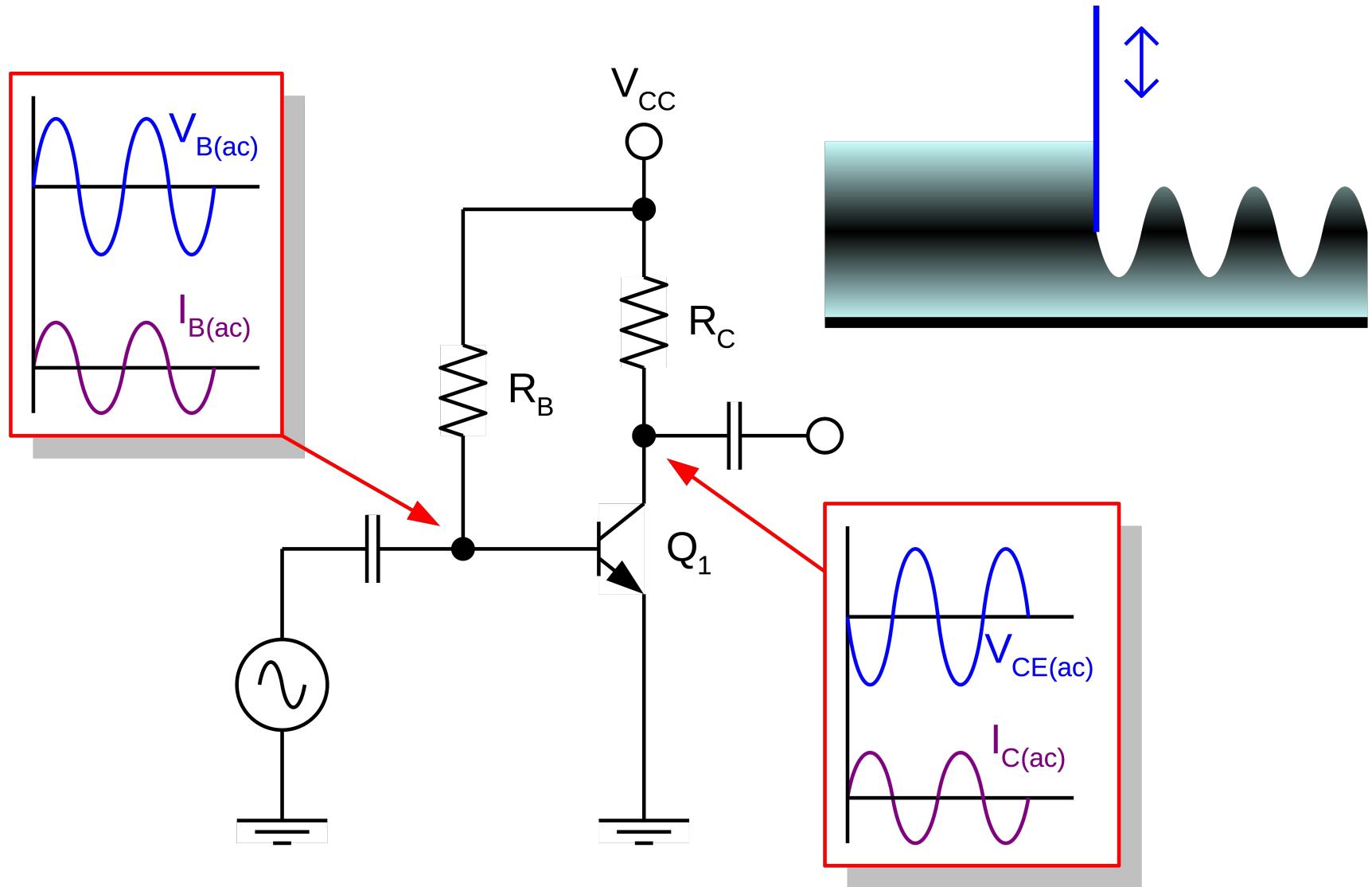


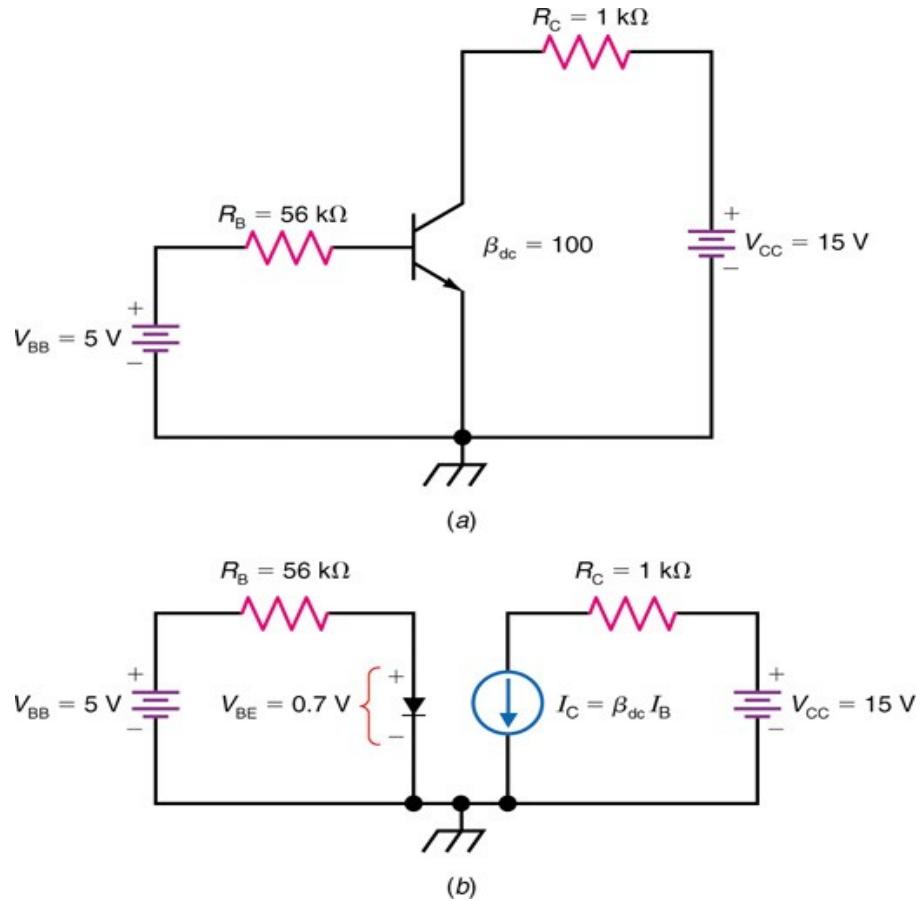
Fig. 5.26(b)

# Typical amplifier operation.



# Transistor Biasing

- Fig. (a) shows the simplest way to bias a transistor, called **base bias**.
- $V_{BB}$  is the base supply voltage, which is used to forward-bias the base-emitter junction.
- $R_B$  is used to provide the desired value of base current.
- $V_{CC}$  is the collector supply voltage, which provides the reverse-bias voltage required for the collector-base junction.
- The collector resistor,  $R_C$ , provides the desired voltage in the collector circuit



# Transistor Biasing: Base Biasing

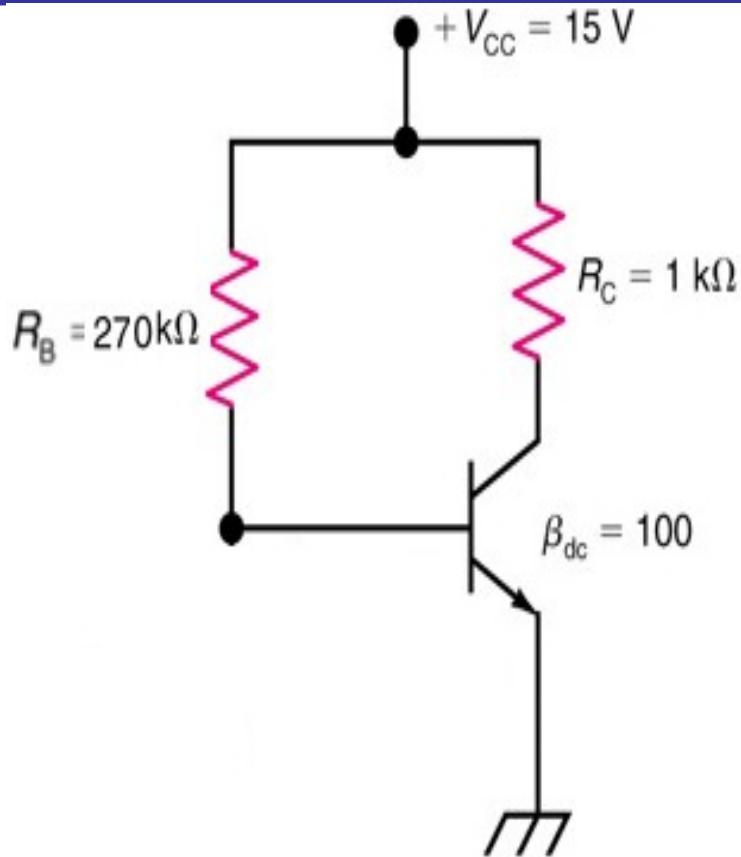
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- A more practical way to provide base bias is to use one power supply.

$$I_B = \frac{V_{CC} - V_{BE}}{R_B}$$

$$I_C \approx \beta_{dc} \times I_B$$

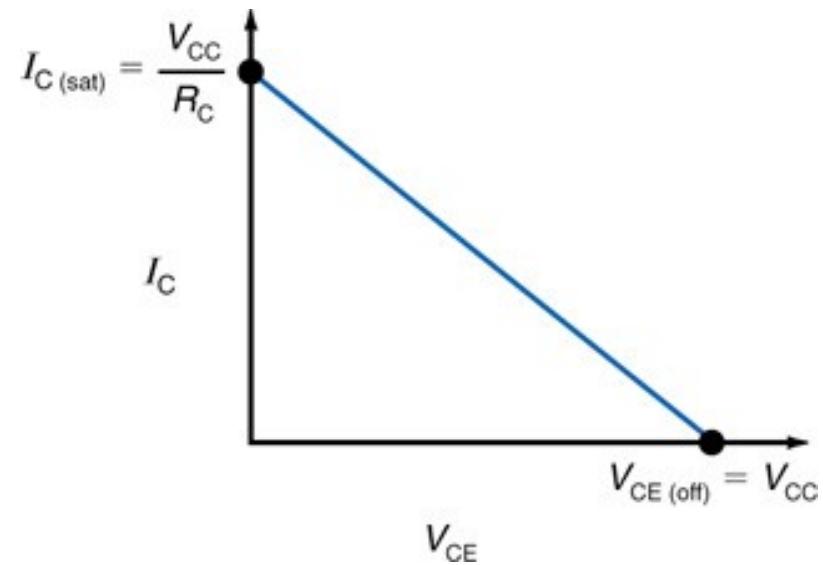
$$V_{CE} \approx V_{CC} - I_C R_C$$



# Transistor Biasing

---

- The **dc load line** is a graph that allows us to determine all possible combinations of  $I_C$  and  $V_{CE}$  for a given amplifier.
- For every value of collector current,  $I_C$ , the corresponding value of  $V_{CE}$  can be found by examining the dc load line.
- A sample dc load line is shown in Fig.



# Transistor Biasing

## Midpoint Bias

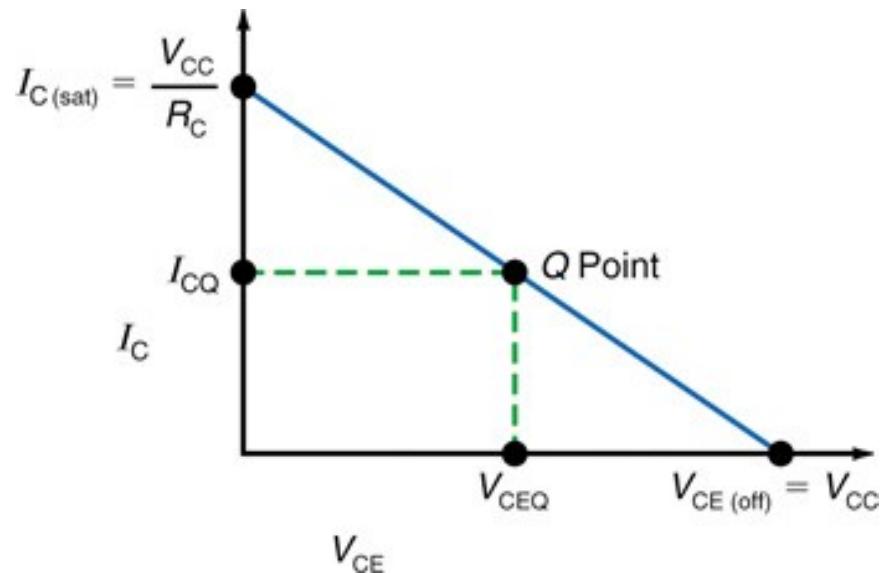
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- Without an ac signal applied to a transistor, specific values of  $I_C$  and  $V_{CE}$  exist at a specific point on a dc load line
  - This specific point is called the Q point (quiescent currents and voltages with no ac input signal)
  - An amplifier is biased such that the Q point is near the center of dc load line
    - $I_{CQ} = \frac{1}{2} I_{C(sat)}$
    - $V_{CEQ} = \frac{1}{2} V_{CC}$
  - Base bias provides a very unstable Q point, because  $I_C$  and  $V_{CE}$  are greatly affected by any change in the transistor's beta value
-

# Transistor Biasing

---

Fig. illustrates a **dc load line** showing the end points  $I_C$  (sat) and  $V_{CE}$  (off), as well as the Q point values  $I_{CQ}$  and  $V_{CEQ}$ .



## **Biassing of BJT**

- Biassing refers to the application of D.C. voltages to setup the operating point in such a way that output signal is undistorted throughout the whole operation.
- Also once selected properly, the Q point should not shift because of change of  $I_C$  due to
  - (I)  $\beta$  variation due to replacement of the transistor of same type
  - (II) Temperature variation

## **Stabilization**

- The process of making operating point independent of temperature changes or variation in transistor parameters is known as stabilization.
- Stabilization of operating point is necessary due to
  - ❖ Temperature dependence of  $I_C$
  - ❖ Individual variations
  - ❖ Thermal runaway

## Stabilization

### Temperature dependence of $I_C$ & Thermal runaway

$$I_C = \beta I_B + (\beta + 1) I_{CBO}$$

- $I_{CBO}$  is strong function of temperature. A rise of  $10^\circ\text{C}$  doubles the  $I_{CBO}$  and  $I_C$  will increase ( $\beta+1$ ) times of  $I_{CBO}$
- The flow of  $I_C$  produce heat within the transistor and raises the transistor temperature further and therefore, further increase in  $I_{CBO}$
- This effect is cumulative and in few seconds, the  $I_C$  may become large enough to burn out the transistor.
- The self destruction of an unstabilized transistor is known as thermal runaway.

## Stability Factor

- The rate of change collector current  $I_C$  with respect to the collector leakage current  $I_{CBO}$  is called stability factor, denoted by  $S$ .

$$S = \left( \frac{dI_C}{dI_{CBO}} \right)$$

Lower the value of  $S$ , better is the stability of the transistor.

## Stability Factor

➤ The rate of change collector current  $I_C$  with respect to the collector leakage current  $I_{CBO}$  at constant  $\beta$  and  $I_B$  is called stability factor, denoted by  $S$ .

$$I_C = \beta I_B + (\beta + 1) I_{CBO} \quad (1)$$

Differentiating equation (1) w.r.t  $I_C$

$$1 = \beta \left( \frac{dI_B}{dI_C} \right) + (\beta + 1) \frac{dI_{CBO}}{dI_C}$$

$$1 = \beta \left( \frac{dI_B}{dI_C} \right) + \frac{(\beta + 1)}{S}$$

$$S = \frac{(\beta + 1)}{1 - \beta \left( \frac{dI_B}{dI_C} \right)}$$

## Different biasing schemes

- (i) Fixed bias (base resistor biasing)
- (ii) Collector base bias
- (iii) Emitter bias
- (iv) Voltage divider bias

## General Formula

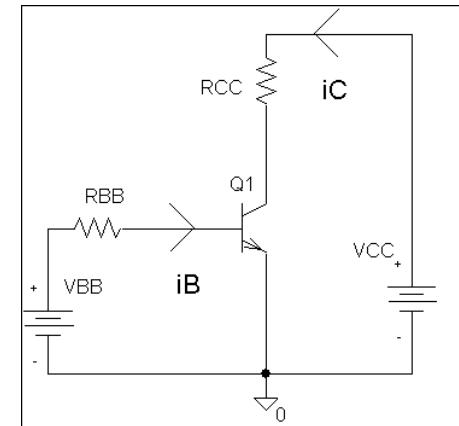
$$S = \frac{1 + \frac{R_B}{R_E}}{1 + (1 - \alpha) \left( \frac{R_b}{R_E} \right)}$$

# Deriving BJT Operating points in Active Region –An Example

In the CE Transistor circuit shown earlier  $V_{BB} = 5V$ ,  $R_{BB} = 107.5 k\Omega$ ,  $R_{CC} = 1 k\Omega$ ,  $V_{CC} = 10V$ . Find  $I_B$ ,  $I_C$ ,  $V_{CE}$ ,  $\beta$  and the transistor power dissipation using the characteristics as shown below

By Applying KVL to the base emitter circuit

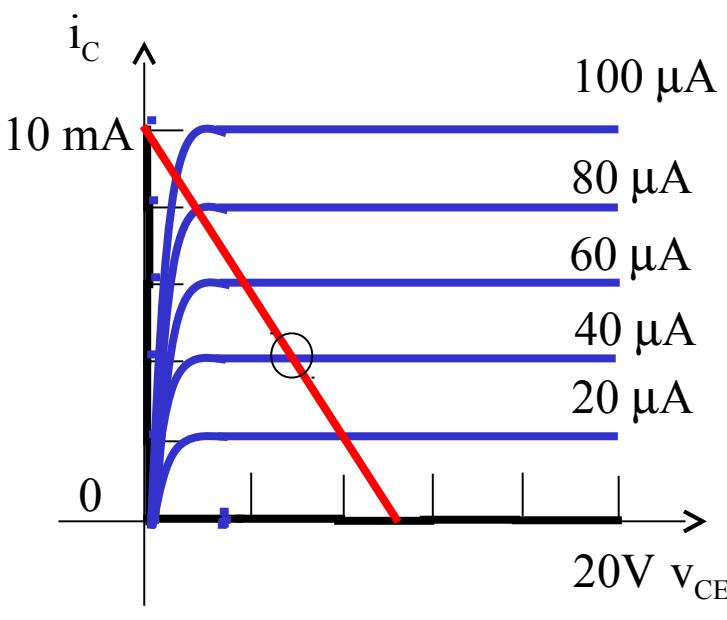
$$I_B = \frac{V_{BB} - V_{BE}}{R_{BB}}$$



By using this equation along with the  $i_B / v_{BE}$  characteristics of the base emitter junction,  $I_B = 40 \mu A$

# Deriving BJT Operating points in Active Region –An Example (2)

By Applying KVL to the collector emitter circuit



$$I_C = \frac{V_{CC} - V_{CE}}{R_{CC}}$$

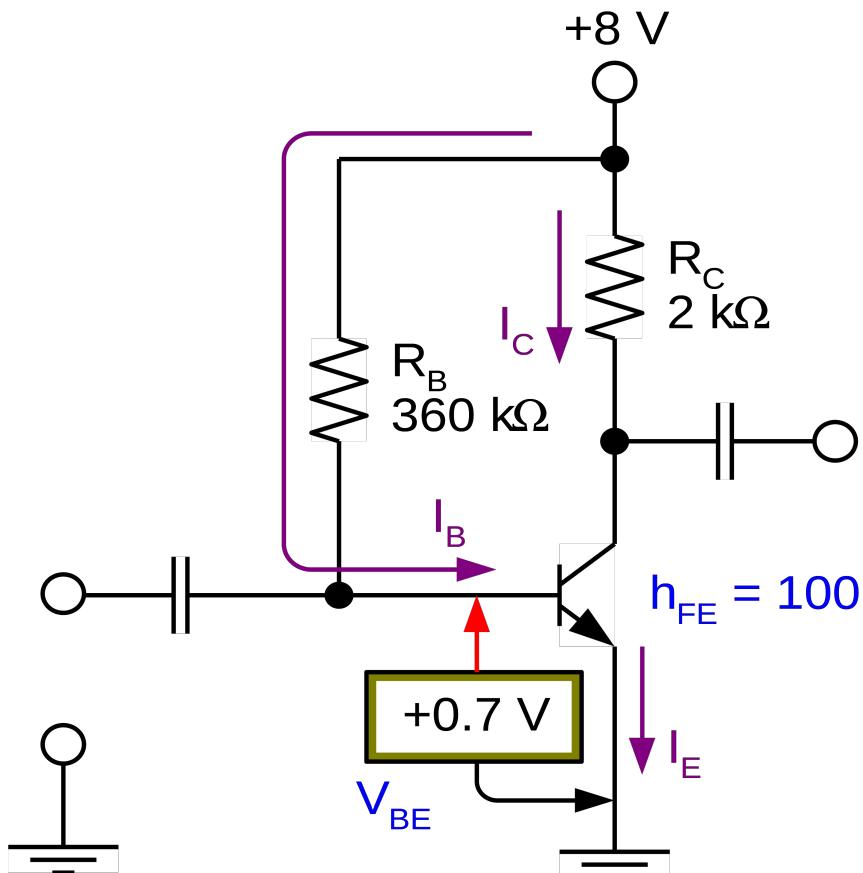
By using this equation along with the  $i_C / v_{CE}$  characteristics of the base collector junction,  $i_C = 4 \text{ mA}$ ,  $V_{CE} = 6 \text{ V}$

$$\beta = \frac{I_C}{I_B} = \frac{4 \text{ mA}}{40 \mu\text{A}} = 100$$

Transistor power dissipation =  $V_{CE} I_C = 24 \text{ mW}$

We can also solve the problem without using the characteristics if  $\beta$  and  $V_{BE}$  values are known

# Example



$$I_B = \frac{V_{CC} - 0.7V}{R_B} = \frac{8V - 0.7V}{360k\Omega}$$

$$= 20.28\mu A$$

$$I_C = h_{FE} I_B = (100)(20.28\mu A)$$

$$= 2.028mA$$

$$V_{CE} = V_{CC} - I_C R_C$$

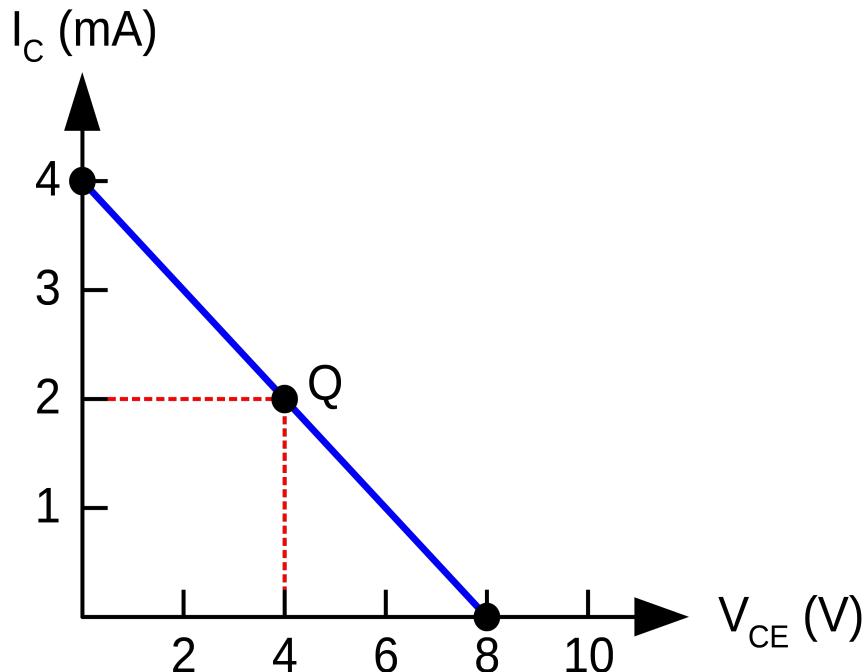
$$= 8V - (2.028mA)(2k\Omega)$$

$$= 3.94V$$

The circuit is midpoint biased.

# Example

Construct the dc load line for the circuit shown in Fig, and plot the Q-point from the values obtained in previous Example. Determine whether the circuit is midpoint biased.

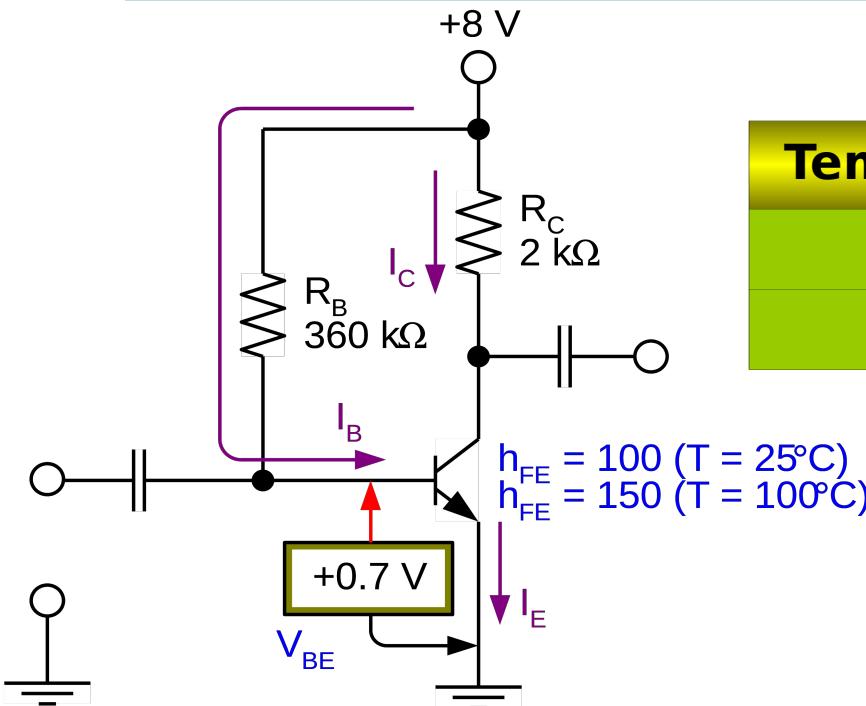


$$I_{C(sat)} = \frac{V_{CC}}{R_C} = \frac{8V}{2k\Omega} = 4mA$$

$$V_{CE(\text{off})} = V_{CC} = 8V$$

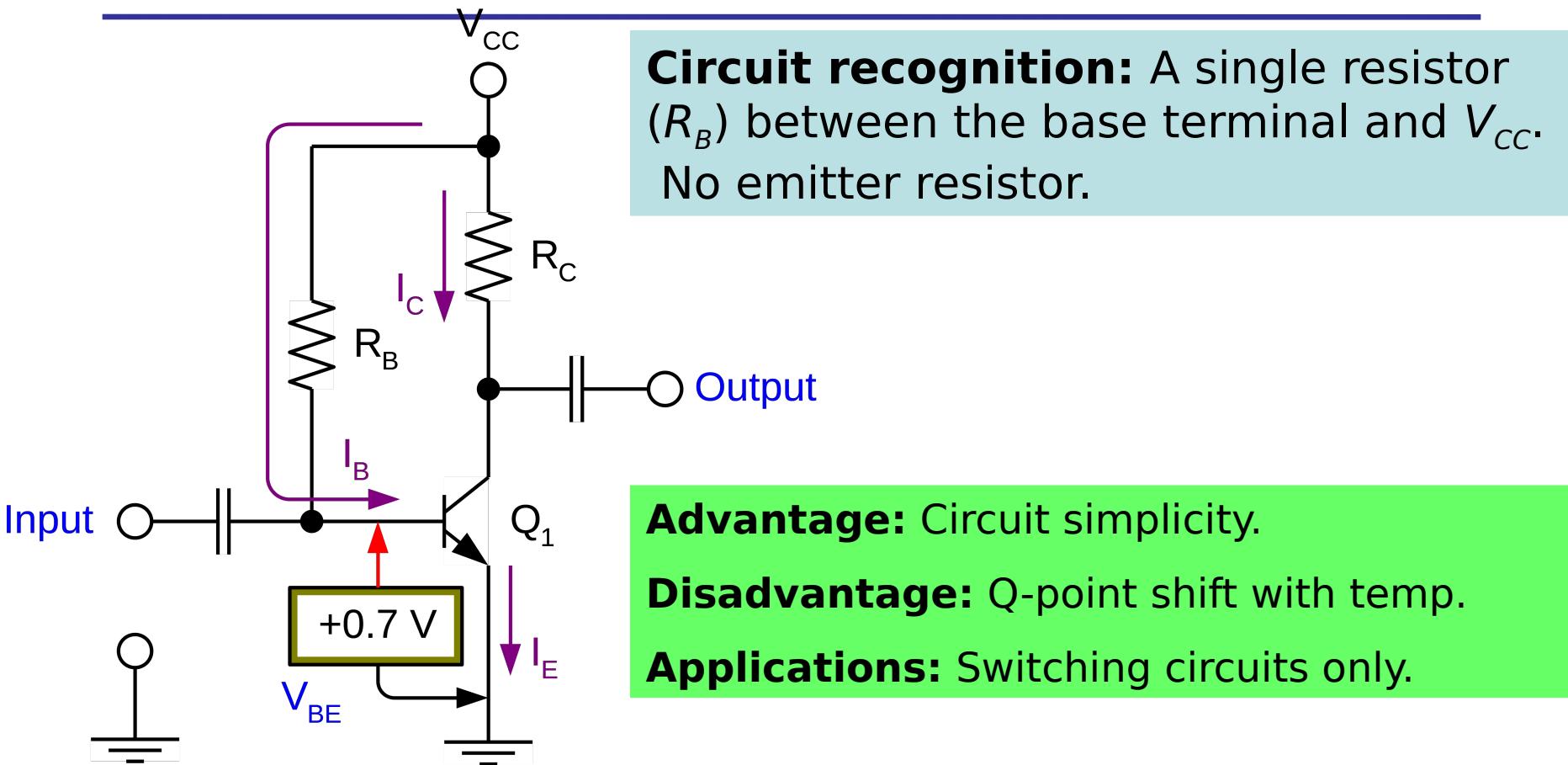
# Example (Q-point shift.)

The transistor in Fig. has values of  $h_{FE} = 100$  when  $T = 25^\circ\text{C}$  and  $h_{FE} = 150$  when  $T = 100^\circ\text{C}$ . Determine the Q-point values of  $I_C$  and  $V_{CE}$  at both of these temperatures.

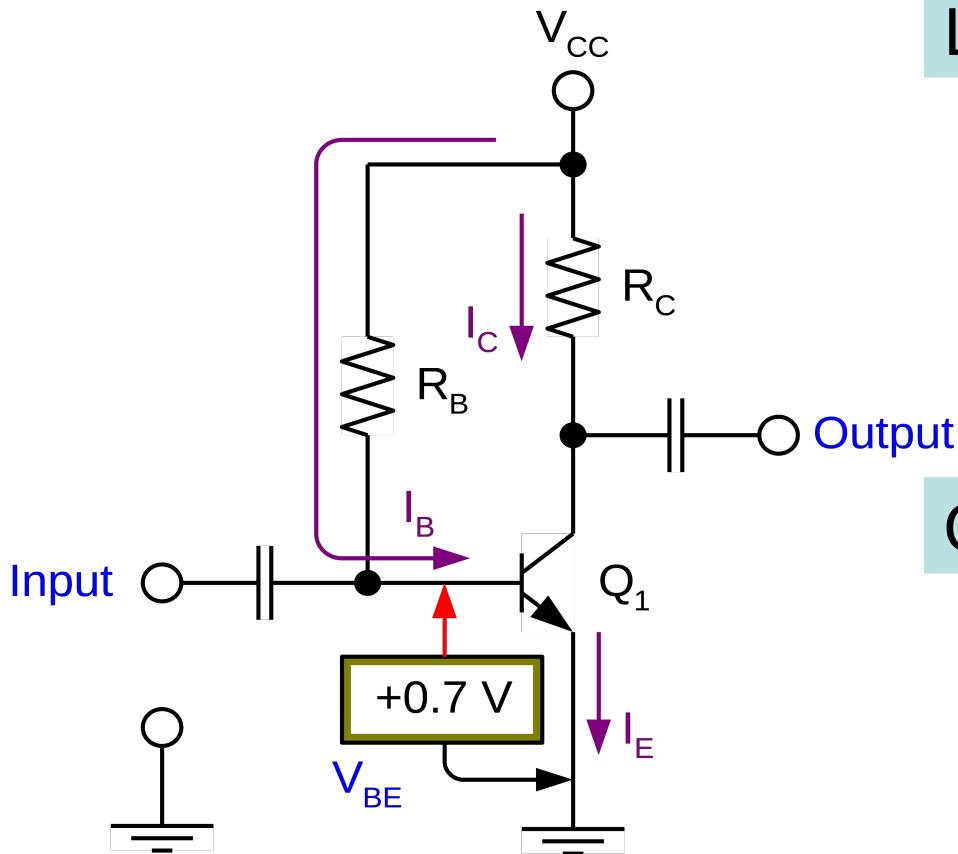


Temp( $^\circ\text{C}$ )	$I_B$ ( $\mu\text{A}$ )	$I_C$ ( $\text{mA}$ )	$V_{CE}$ ( $\text{V}$ )
25	20.28	2.028	3.94
100	20.28	3.04	1.92

# Base bias characteristics. (1)



# Base bias characteristics. (2)



Load line equations:

$$I_{C(\text{sat})} \cong \frac{V_{CC}}{R_C}$$

$$V_{CE(\text{off})} = V_{CC}$$

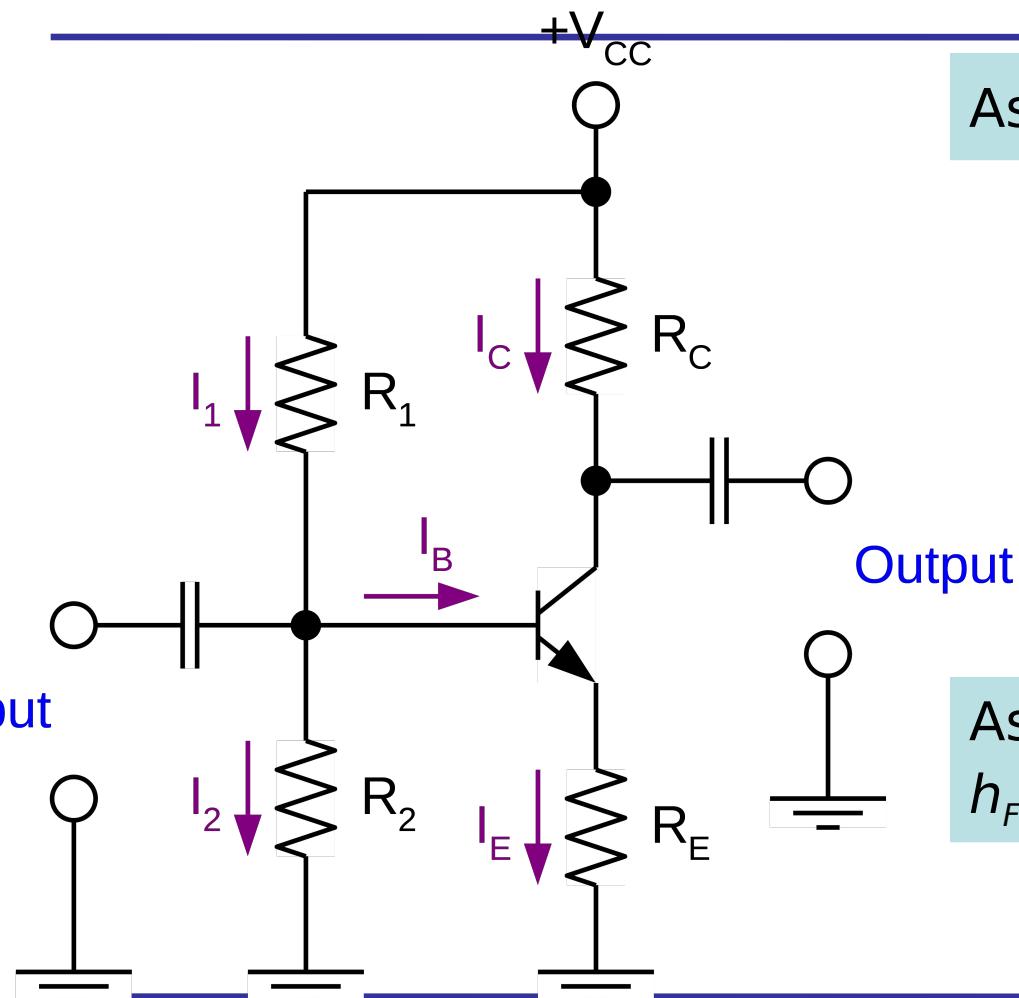
Q-point equations:

$$I_B = \frac{V_{CC} - V_{BE}}{R_B}$$

$$I_C = h_{FE} I_B$$

$$V_{CE} = V_{CC} - I_C R_C$$

# Voltage divider bias. (1)



Assume that  $I_2 > 10I_B$ .

$$V_B = \frac{R_2}{R_1 + R_2} V_{CC}$$

$$V_E = V_B - 0.7V$$

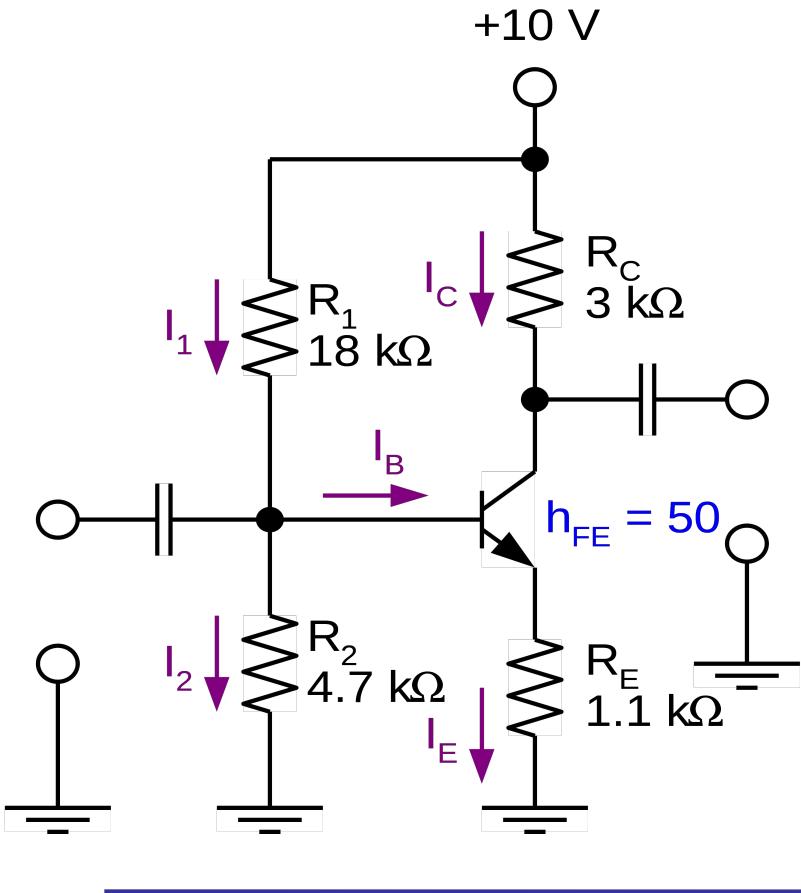
$$I_E = \frac{V_E}{R_E}$$

Assume that  $I_{CQ} \approx I_E$  (or  $h_{FE} \gg 1$ ). Then

$$V_{CEQ} = V_{CC} - I_{CQ} (R_C + R_E)$$

# Example (1)

Determine the values of  $I_{CQ}$  and  $V_{CEQ}$  for the circuit shown in Fig.



$$V_B = V_{CC} \frac{R_2}{R_1 + R_2}$$

$$= (10V) \frac{4.7k\Omega}{22.7k\Omega} = 2.07V$$

$$V_E = V_B - 0.7V$$

$$= 2.07V - 0.7V = 1.37V$$

Because  $I_{CQ} \approx I_E$  (or  $h_{FE} \gg 1$ ),

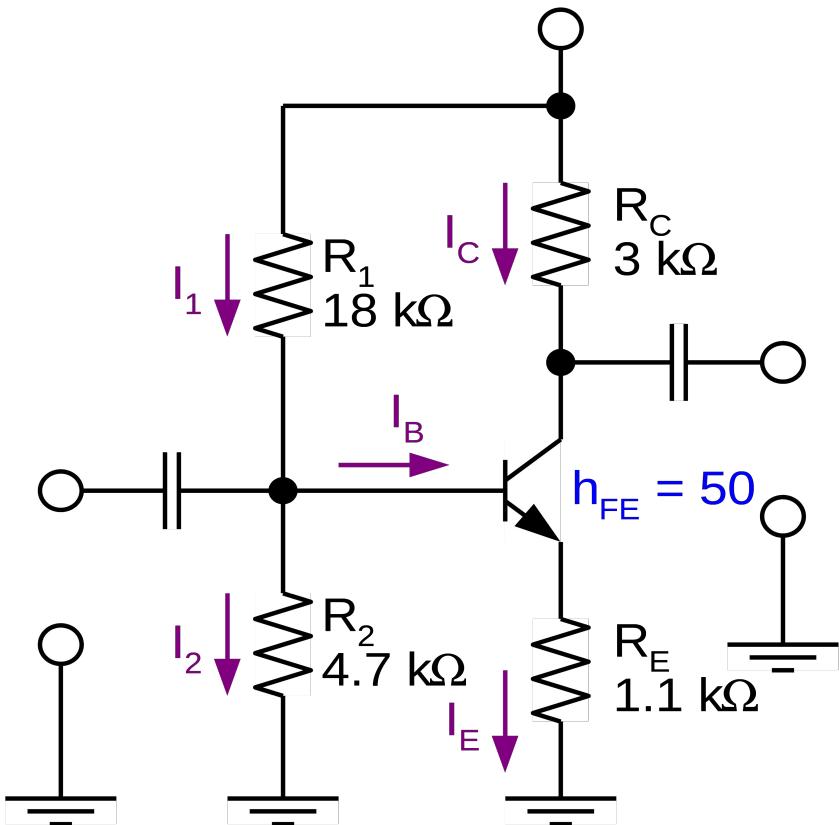
$$I_{CQ} \approx \frac{V_E}{R_E} = \frac{1.37V}{1.1k\Omega} = 1.25mA$$

$$V_{CEQ} = V_{CC} - I_{CQ}(R_C + R_E)$$

$$= 10V - (1.25mA)(4.1k\Omega) = 4.87V$$

# Example (2)

Verify that  $I_2 > 10 I_B$ .



$$I_2 = \frac{V_B}{R_2} = \frac{2.07\text{V}}{4.7\text{k}\Omega} = 440.4\mu\text{A}$$

$$\begin{aligned} I_B &= \frac{I_E}{h_{FE} + 1} = \frac{1.25\text{mA}}{50+1} \\ &= 24.51\mu\text{A} \end{aligned}$$

$$\therefore I_2 > 10 I_B$$

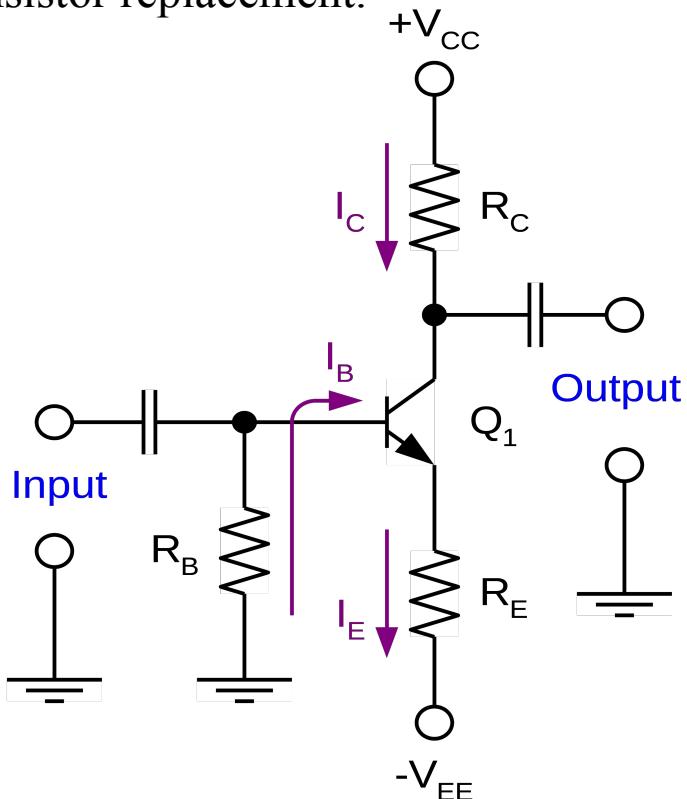
# Other Transistor Biasing Circuits

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- Emitter-bias circuits
- Feedback-bias circuits
  - Collector-feedback bias
  - Emitter-feedback bias

# Emitter bias.

- Both positive and negative power supplies are available
- Emitter bias** provides a solid Q point that fluctuates very little with temperature variation and transistor replacement.



Assume that the transistor operation is in active region.

$$I_B = \frac{V_{EE} - 0.7V}{R_B + (h_{FE} + 1) R_E}$$

$$I_C = h_{FE} I_B$$

$$I_E = (h_{FE} + 1) I_B$$

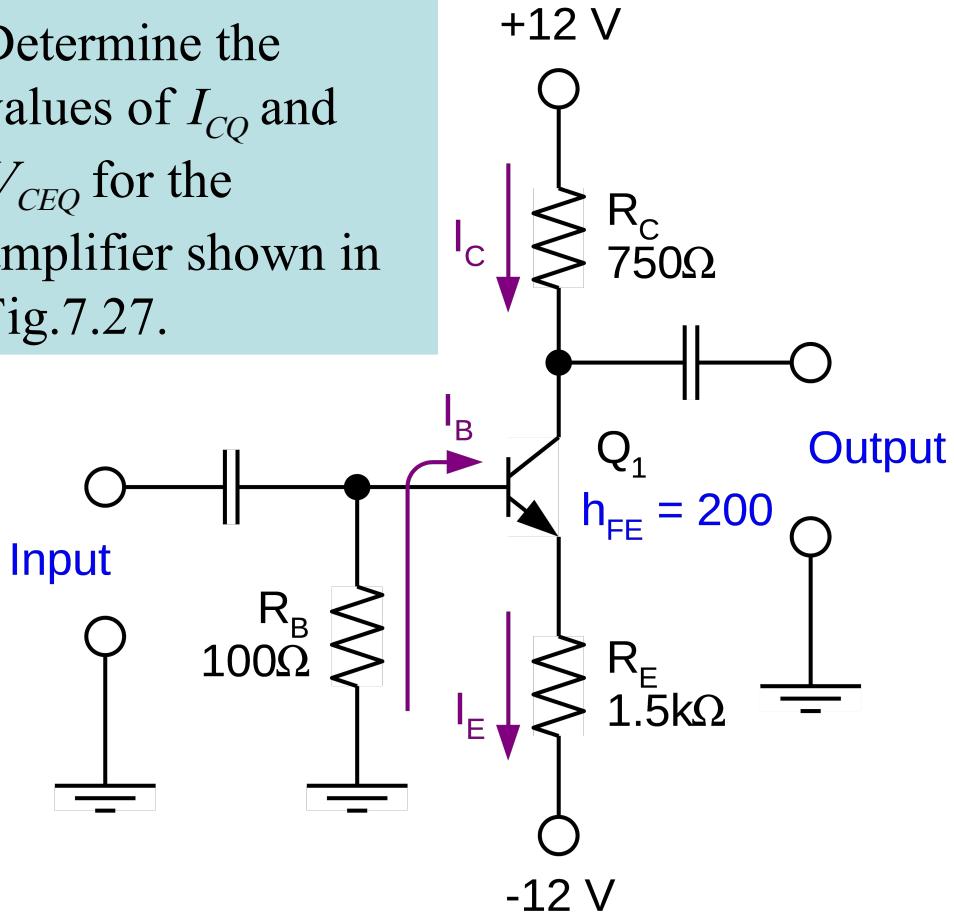
$$V_{CE} = V_{CC} - I_C R_C - I_E R_E + V_{EE}$$

Assume that  $h_{FE} \gg 1$ .

$$V_{CE} \approx V_{CC} - I_C (R_C + R_E) + V_{EE}$$

# Example

Determine the values of  $I_{CQ}$  and  $V_{CEQ}$  for the amplifier shown in Fig. 7.27.



$$I_B = \frac{12V - 0.7V}{R_B + (h_{FE} + 1)R_E}$$

$$= \frac{11.3V}{100\Omega + 201 \times 1.5k\Omega} = 37.47\mu A$$

$$I_{CQ} = h_{FE} I_B = 200 \times 37.47\mu A$$

$$= 7.49mA$$

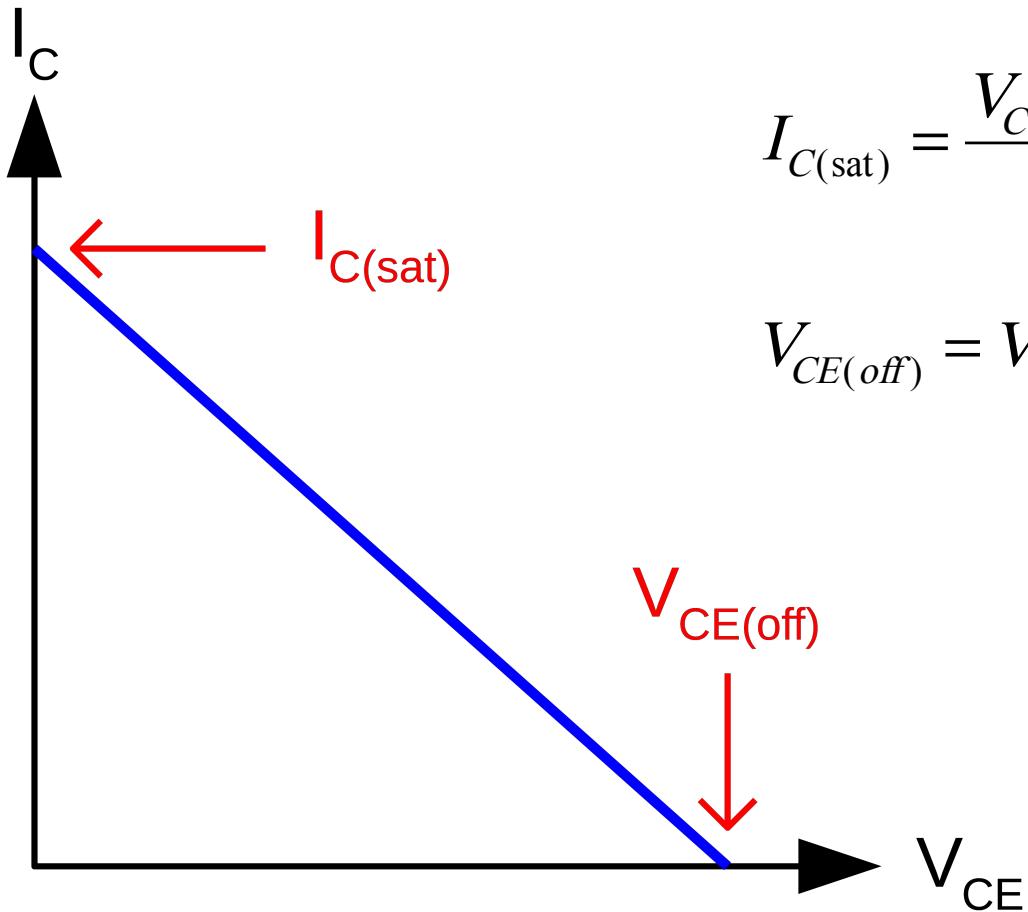
$$V_{CEQ} \approx V_{CC} - I_C (R_C + R_E) - (-V_{EE})$$

$$= 24V - 7.49mA (750\Omega + 1.5k\Omega)$$

$$= 7.14V$$

# Load Line for Emitter-Bias Circuit

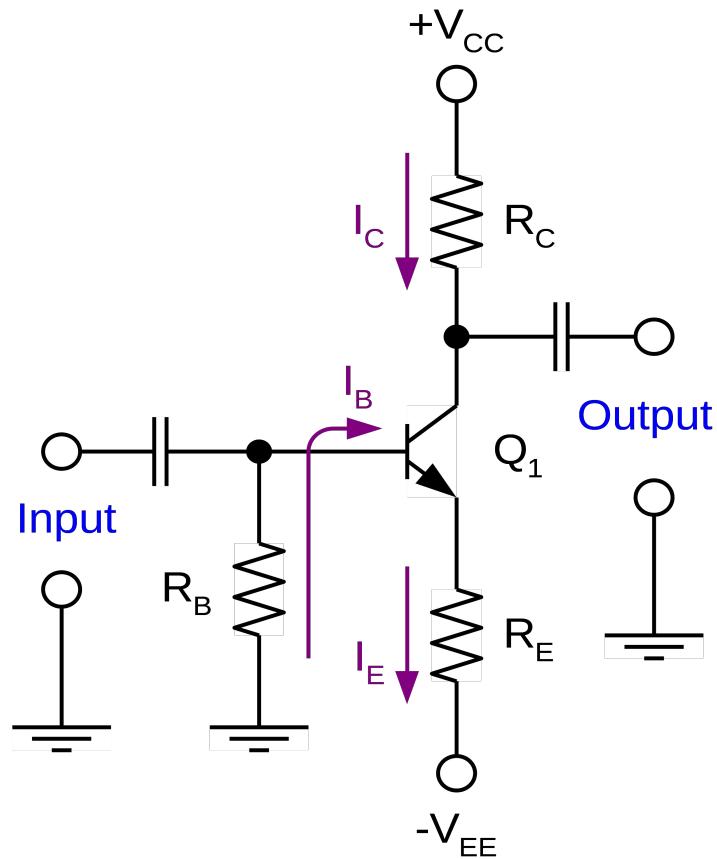
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$$I_{C(sat)} = \frac{V_{CC} - (-V_{EE})}{R_C + R_E} = \frac{V_{CC} + V_{EE}}{R_C + R_E}$$

$$V_{CE(off)} = V_{CC} - (-V_{EE}) = V_{CC} + V_{EE}$$

# Emitter-bias characteristics. (1)



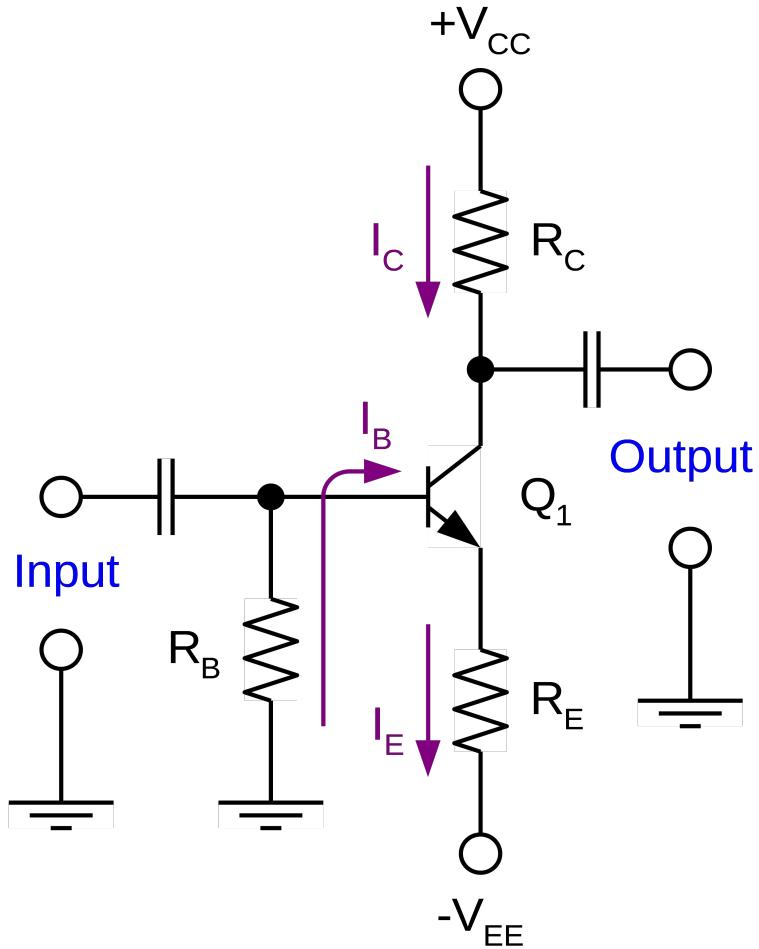
**Circuit recognition:** A split (dual-polarity) power supply and the base resistor is connected to ground.

**Advantage:** The circuit Q-point values are stable against changes in  $h_{FE}$ .

**Disadvantage:** Requires the use of dual-polarity power supply.

**Applications:** Used primarily to bias linear amplifiers.

# Emitter-bias characteristics. (2)



Load line equations:

$$I_{C(\text{sat})} = \frac{V_{CC} + V_{EE}}{R_C + R_E}$$

$$V_{CE(\text{off})} = V_{CC} + V_{EE}$$

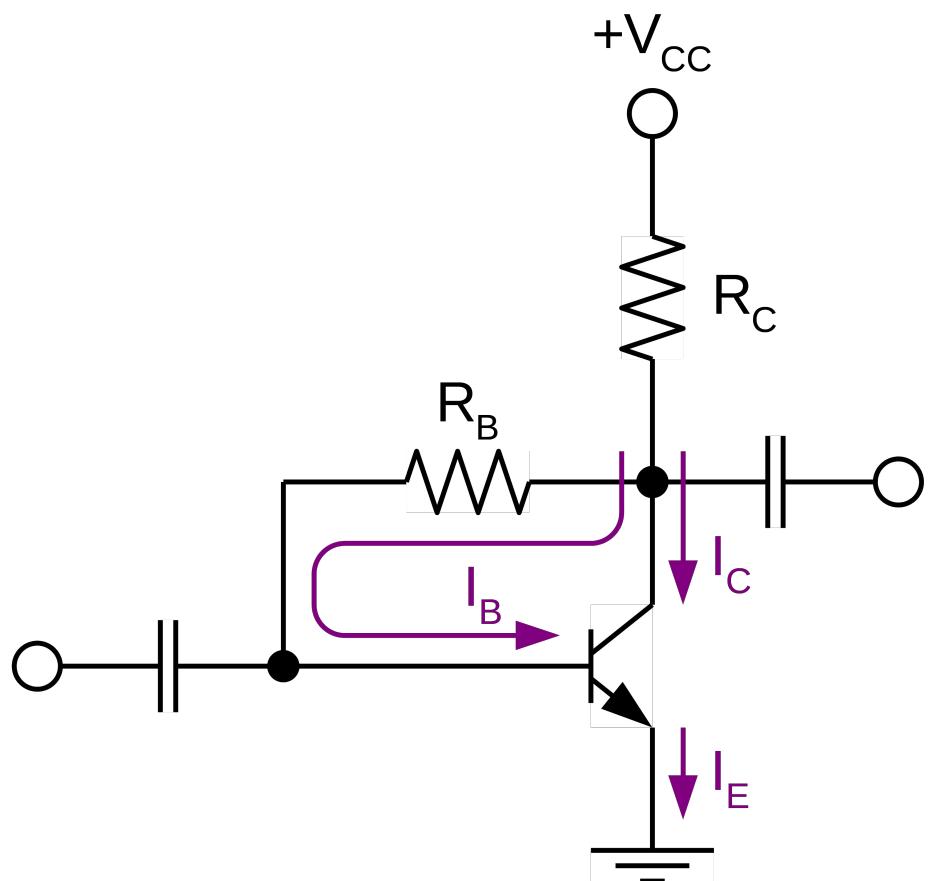
Q-point equations:

$$I_{CQ} = (h_{FE}) \frac{-V_{BE} + V_{EE}}{R_B + (h_{FE} + 1) R_E}$$

$$V_{CEQ} \cong V_{CC} - I_{CQ} (R_C + R_E) + V_{EE}$$

# Collector-feedback bias.

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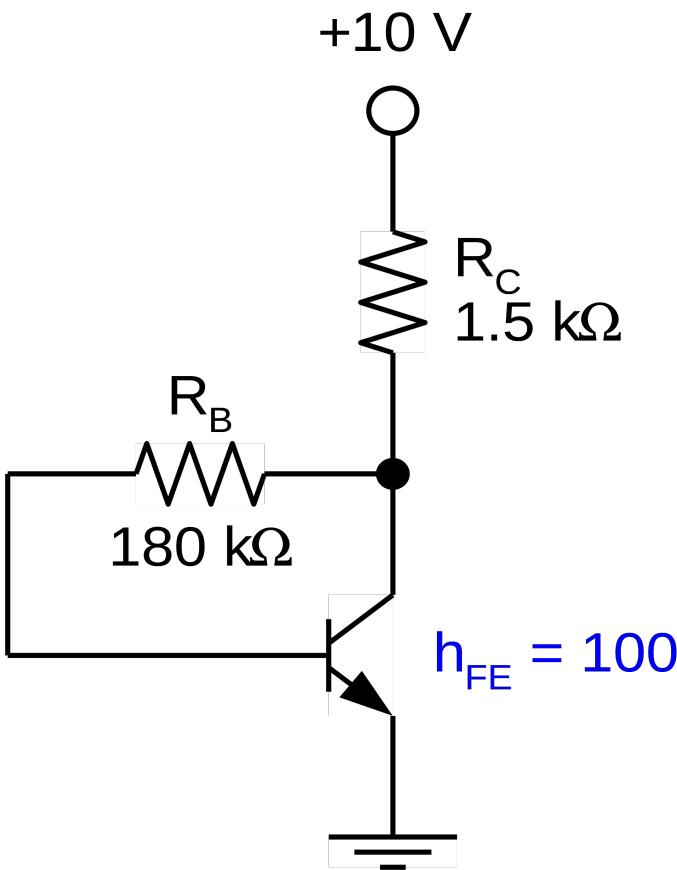
$$V_{CC} = (I_C + I_B) R_C + I_B R_B + V_{BE}$$

$$I_B = \frac{V_{CC} - V_{BE}}{(h_{FE} + 1)R_C + R_B}$$

$$I_{CQ} = h_{FE} I_B$$

$$\begin{aligned} V_{CEQ} &= V_{CC} - (h_{FE} + 1) I_B R_C \\ &\cong V_{CC} - I_{CQ} R_C \end{aligned}$$

# Example



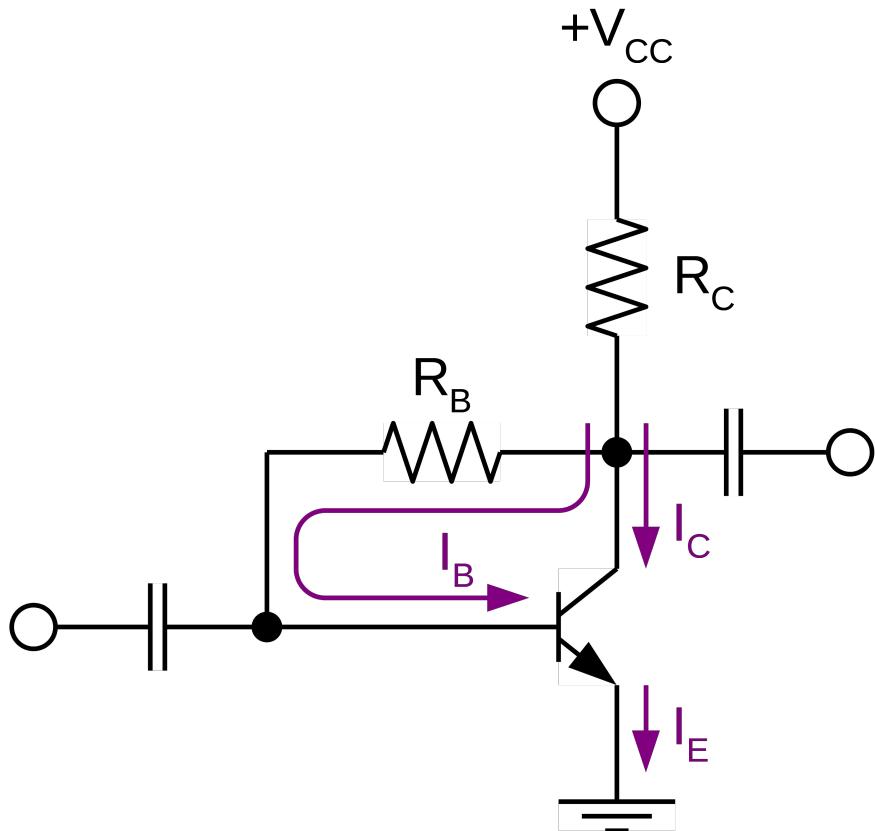
Determine the values of  $I_{CQ}$  and  $V_{CEQ}$  for the amplifier shown in Fig. 7.30.

$$I_B = \frac{V_{CC} - V_{BE}}{R_B + (h_{FE} + 1) R_C}$$
$$= \frac{10\text{V} - 0.7\text{V}}{180\text{k}\Omega + 101 \times 1.5\text{k}\Omega} = 28.05\mu\text{A}$$

$$I_{CQ} = h_{FE} I_B = 100 \times 28.05\mu\text{A}$$
$$= 2.805\text{mA}$$

$$V_{CEQ} = V_{CC} - (h_{FE} + 1) I_B R_C$$
$$= 10\text{V} - 101 \times 28.05\mu\text{A} \times 1.5\text{k}\Omega$$
$$= 5.75\text{V}$$

# Circuit Stability of Collector-Feedback Bias



$h_{FE}$  increases



$I_C$  increases (if  $I_B$  is the same)



$V_{CE}$  decreases

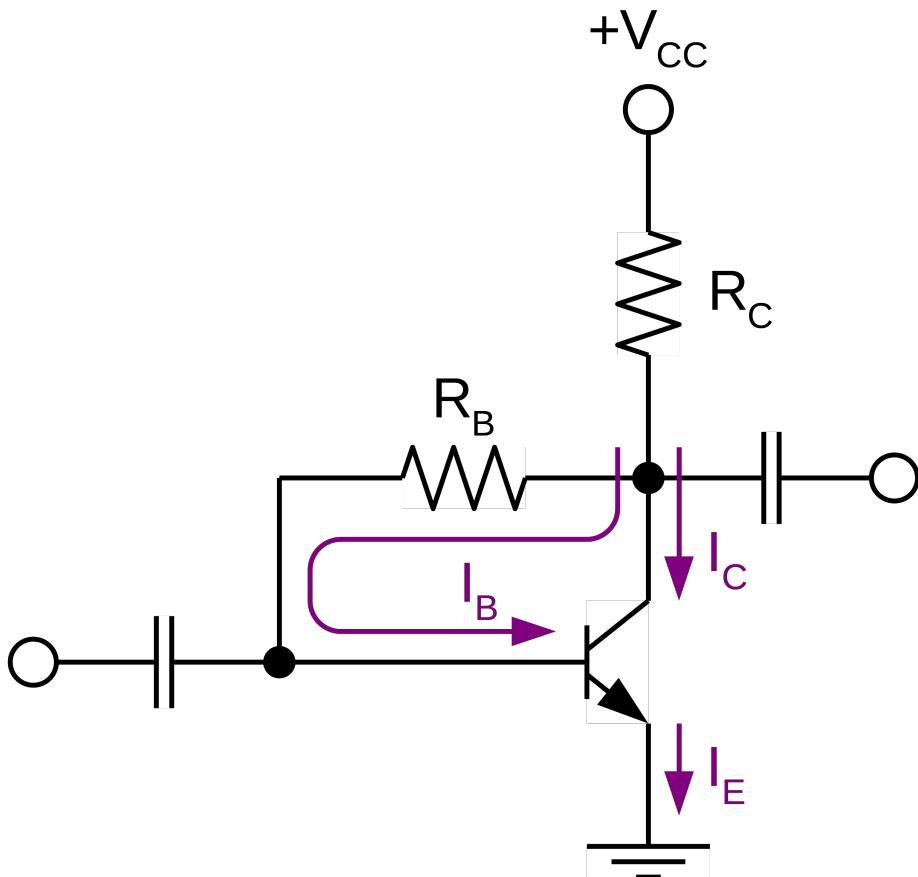


$I_B$  decreases

$I_C$  does not increase that much.

Good Stability. Less dependent on  $h_{FE}$  and temperature.

# Collector-Feedback Characteristics (1)



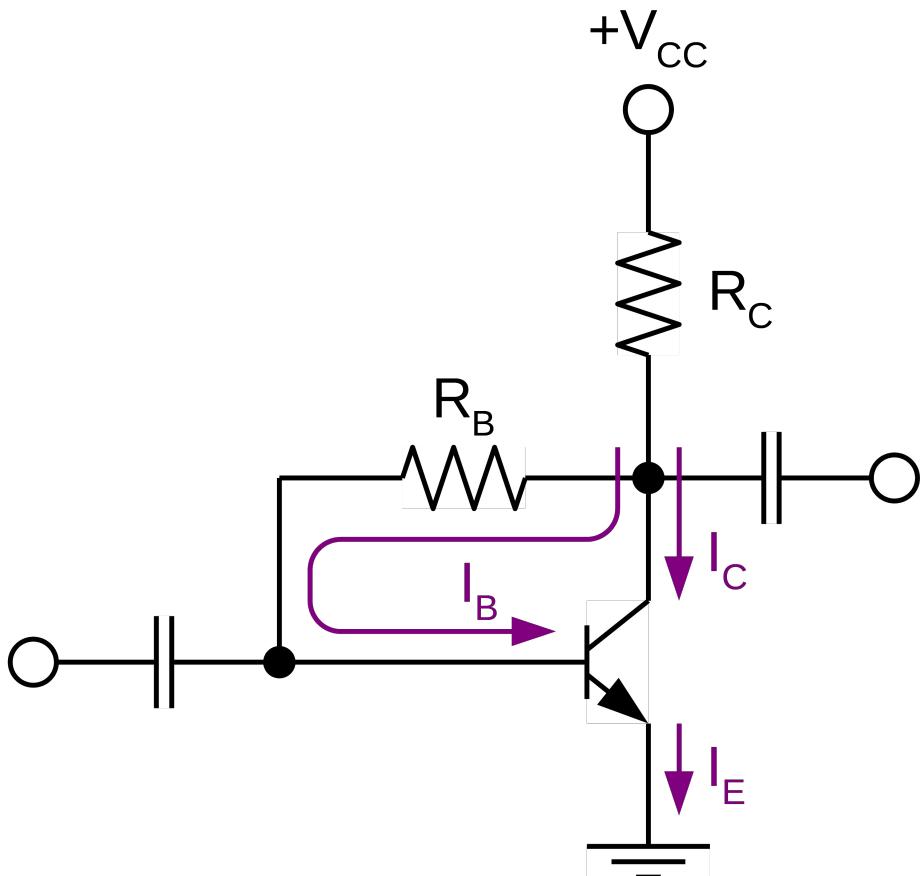
**Circuit recognition:** The base resistor is connected between the base and the collector terminals of the transistor.

**Advantage:** A simple circuit with relatively stable Q-point.

**Disadvantage:** Relatively poor ac characteristics.

**Applications:** Used primarily to bias linear amplifiers.

# Collector-Feedback Characteristics (2)



Q-point relationships:

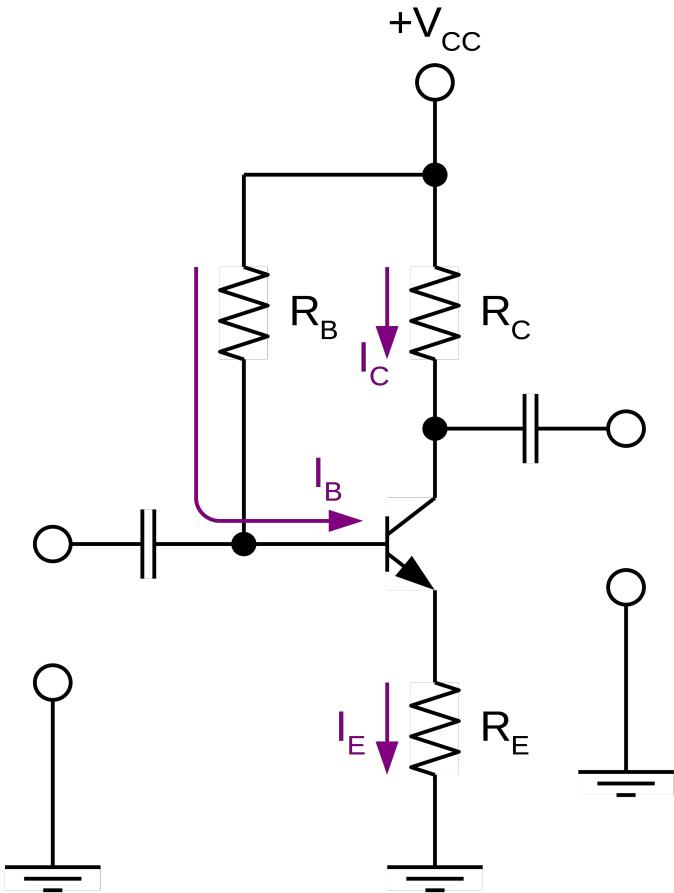
$$I_B = \frac{V_{CC} - V_{BE}}{(h_{FE} + 1)R_C + R_B}$$

$$I_{CQ} = h_{FE} I_B$$

$$V_{CEQ} \cong V_{CC} - I_{CQ} R_C$$

# Emitter-feedback bias.

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$$I_B = \frac{V_{CC} - V_{BE}}{R_B + (h_{FE} + 1) R_E}$$

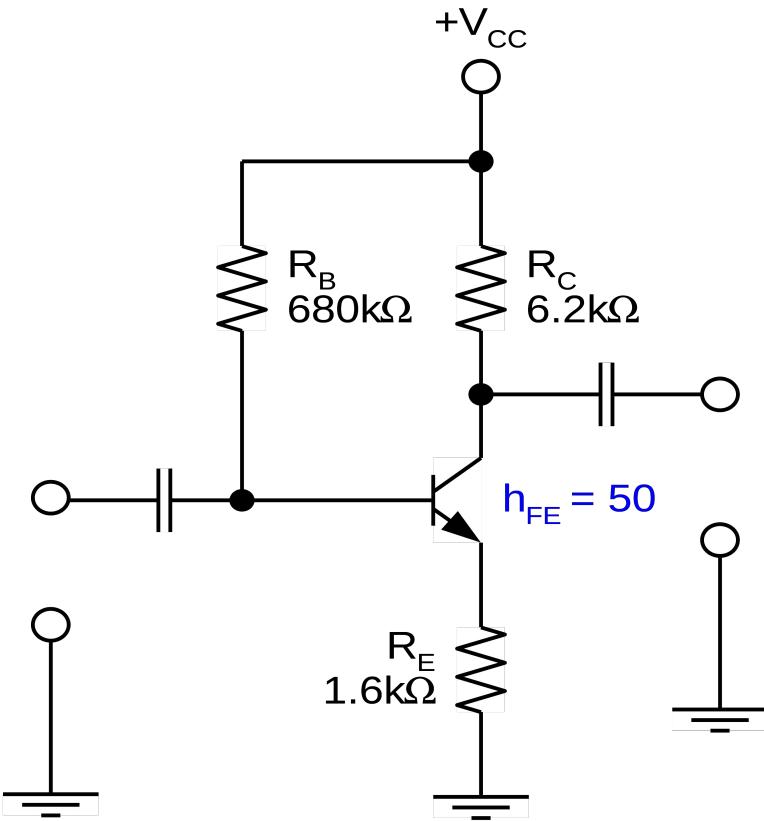
$$I_{CQ} = h_{FE} I_B$$

$$I_E = (h_{FE} + 1) I_B$$

$$\begin{aligned} V_{CEQ} &= V_{CC} - I_C R_C - I_E R_E \\ &\cong V_{CC} - I_{CQ} (R_C + R_E) \end{aligned}$$

# Example

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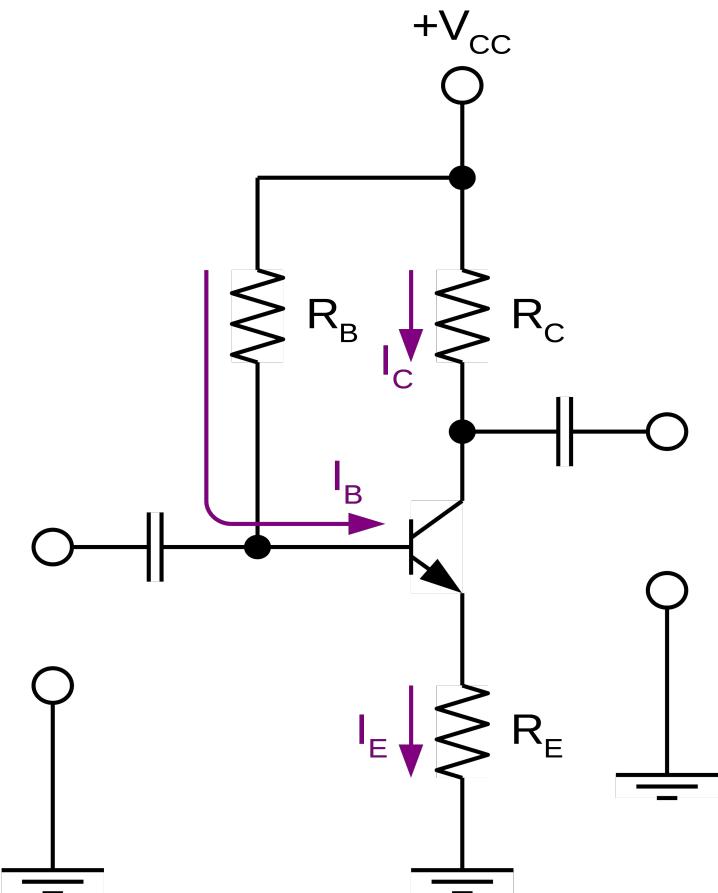


$$I_B = \frac{V_{CC} - V_{BE}}{R_B + (h_{FE} + 1) R_E} = \frac{16\text{V} - 0.7\text{V}}{680\text{k}\Omega + 51 \times 1.6\text{k}\Omega} = 20.09\mu\text{A}$$

$$I_{CQ} = h_{FE} I_B = 50 \times 20.09\mu\text{A} = 1\text{mA}$$

$$V_{CEQ} \cong V_{CC} - I_{CQ} (R_C + R_E) = 16\text{V} - (1\text{mA}) (7.8\text{k}\Omega) = 8.2\text{V}$$

# Circuit Stability of Emitter-Feedback Bias



$h_{FE}$  increases

$I_C$  increases (if  $I_B$  is the same)

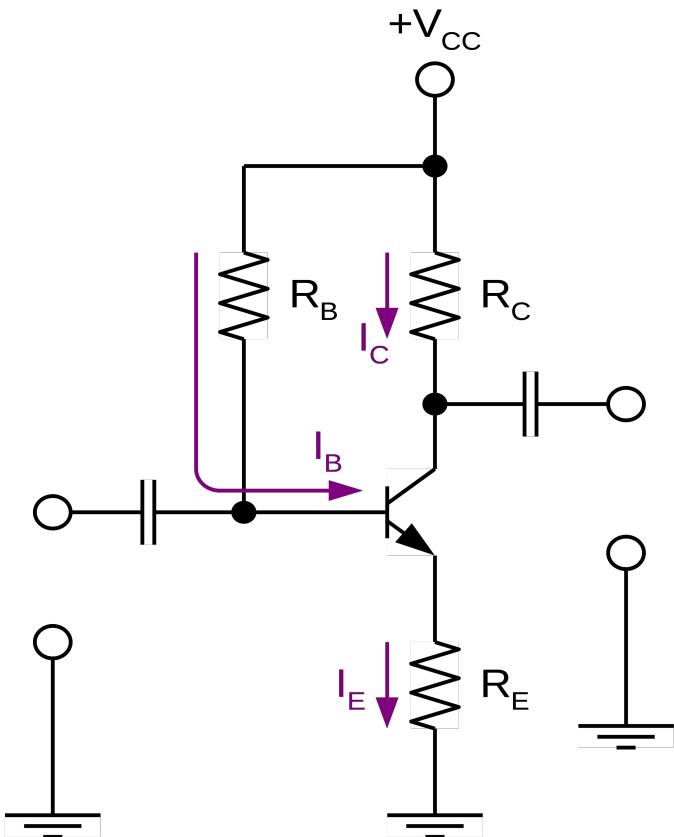
$V_E$  increases

$I_B$  decreases

$I_C$  does not increase that much.

$I_C$  is less dependent on  $h_{FE}$  and temperature.

# Emitter-Feedback Characteristics (1)



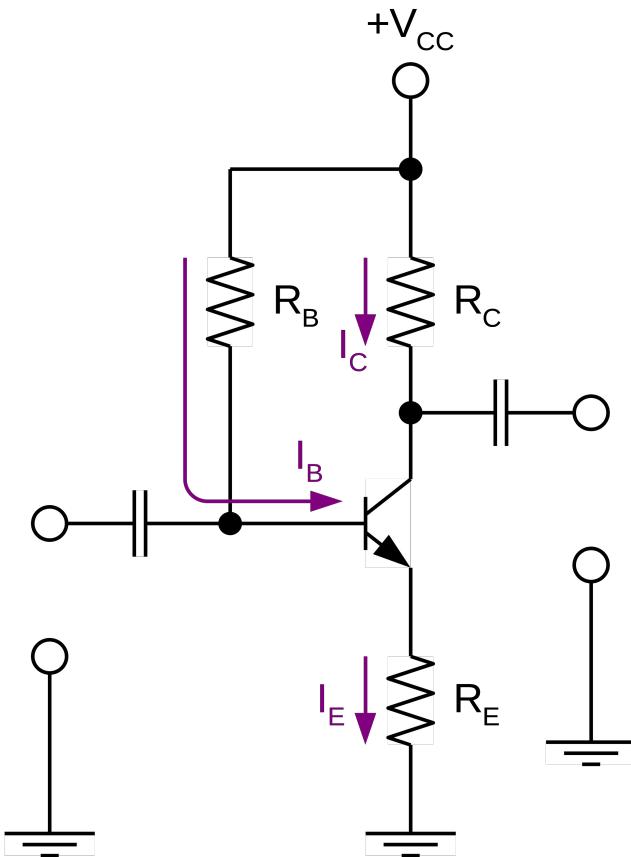
**Circuit recognition:** Similar to voltage divider bias with  $R_2$  missing (or base bias with  $R_E$  added).

**Advantage:** A simple circuit with relatively stable Q-point.

**Disadvantage:** Requires more components than collector-feedback bias.

**Applications:** Used primarily to bias linear amplifiers.

# Emitter-Feedback Characteristics (2)



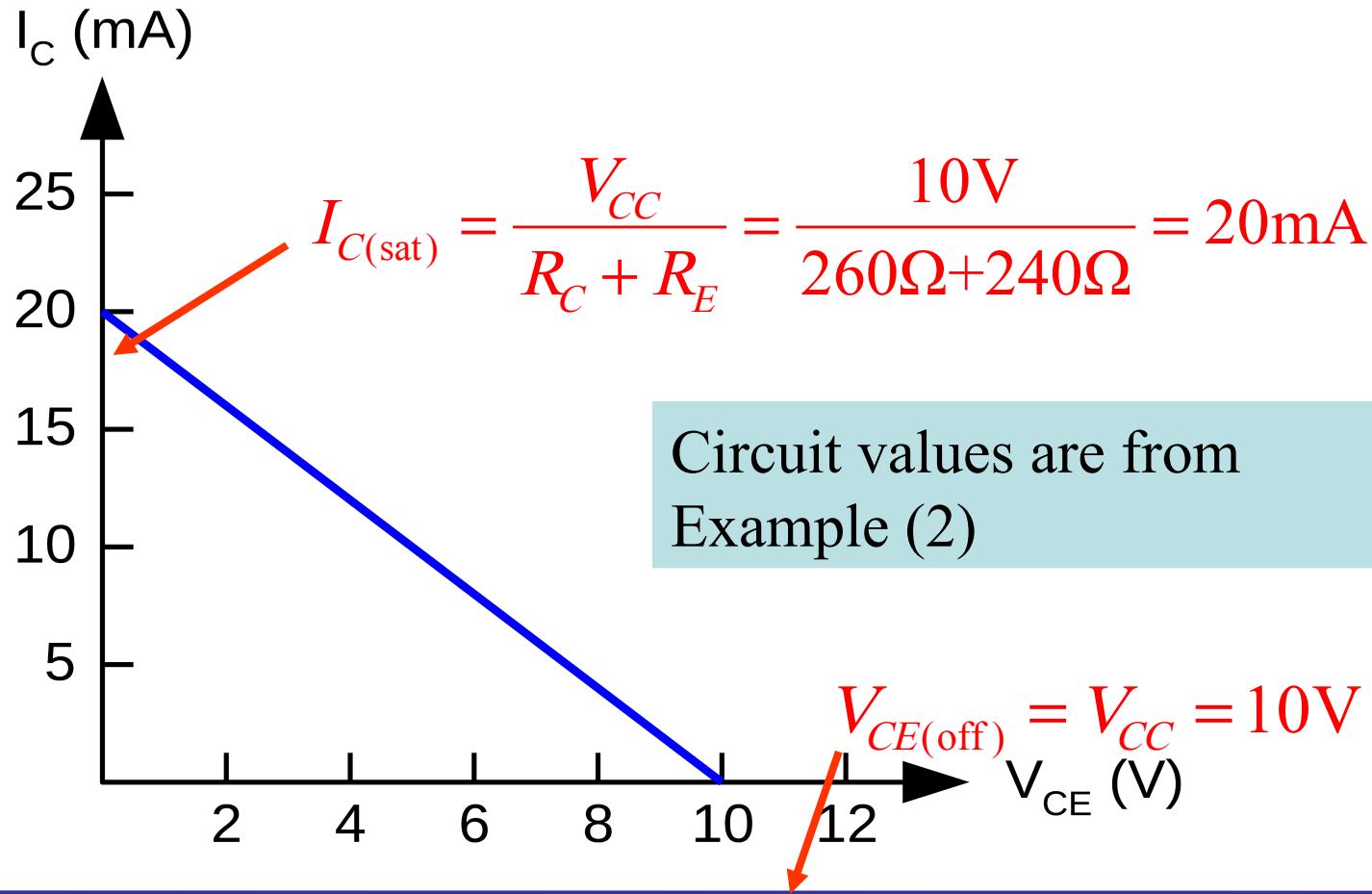
Q-point relationships:

$$I_B = \frac{V_{CC} - V_{BE}}{R_B + (h_{FE} + 1)R_E}$$

$$I_{CQ} = h_{FE} I_B$$

$$V_{CEQ} \cong V_{CC} - I_{CQ} ( R_C + R_E )$$

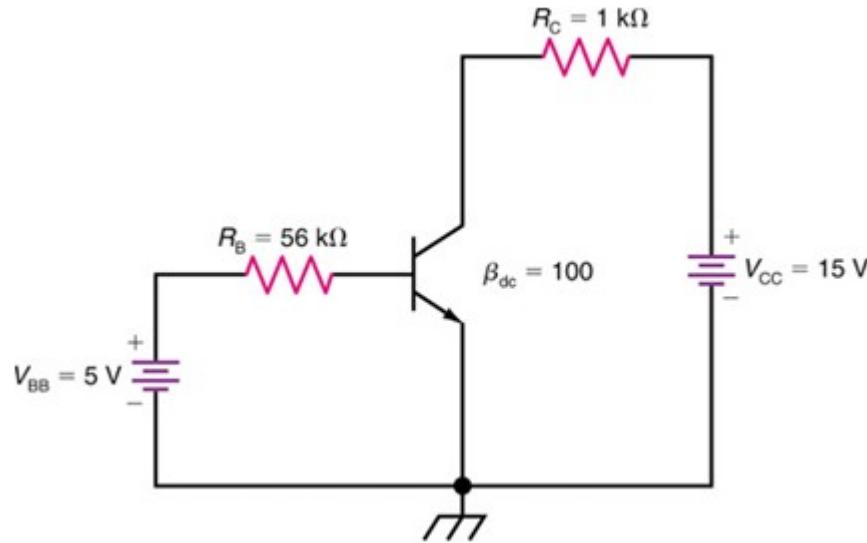
# Load line for voltage divider bias circuit.



# Base Bias - Example 1

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- Solve for  $I_B$ ,  $I_C$  and  $V_{CE}$
- Construct a dc load line showing the values of  $I_{C(sat)}$ ,  $V_{CE(off)}$ ,  $I_{CQ}$  and  $V_{CEQ}$

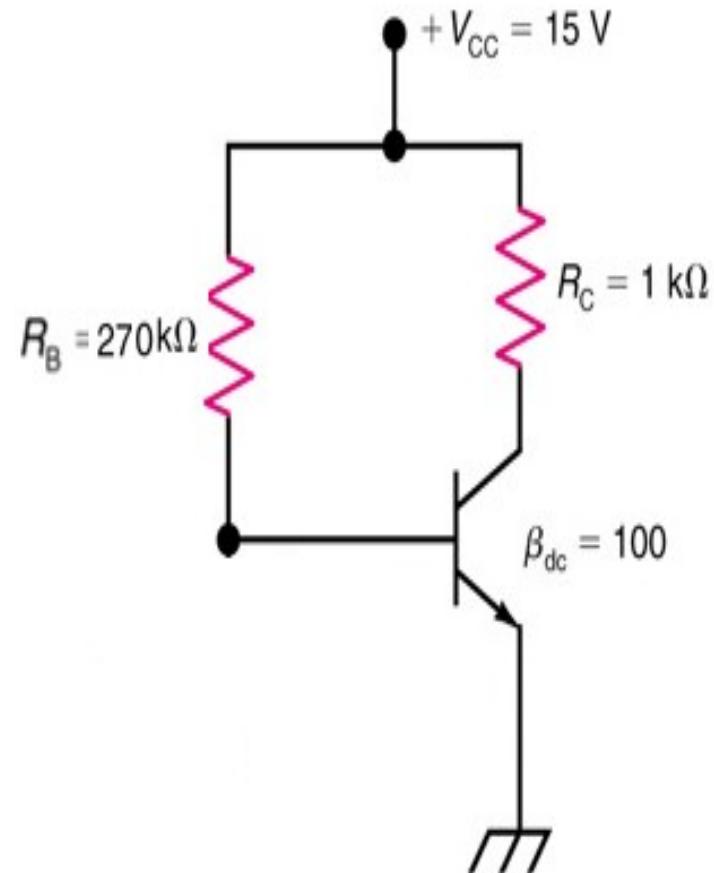


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# Base Bias - Example 2

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- Solve for  $I_B$ ,  $I_C$  and  $V_{CE}$
- Construct a dc load line showing the values of  $I_{C(sat)}$ ,  $V_{CE(off)}$ ,  $I_{CQ}$  and  $V_{CEQ}$



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# Transistor Biasing

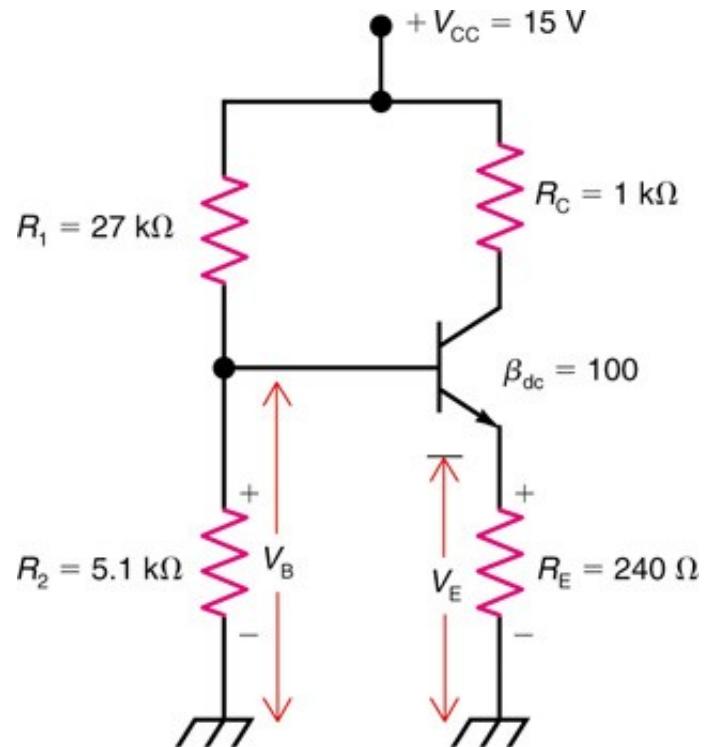
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- The most popular way to bias a transistor is with **voltage-divider bias**.
- The advantage of voltage-divider bias lies in its stability.
- An example of voltage-divider bias is shown in Fig.

$$V_B = \frac{R_2}{R_1 + R_2} \times V_{CC}$$

$$V_E = V_B - V_{BE}$$

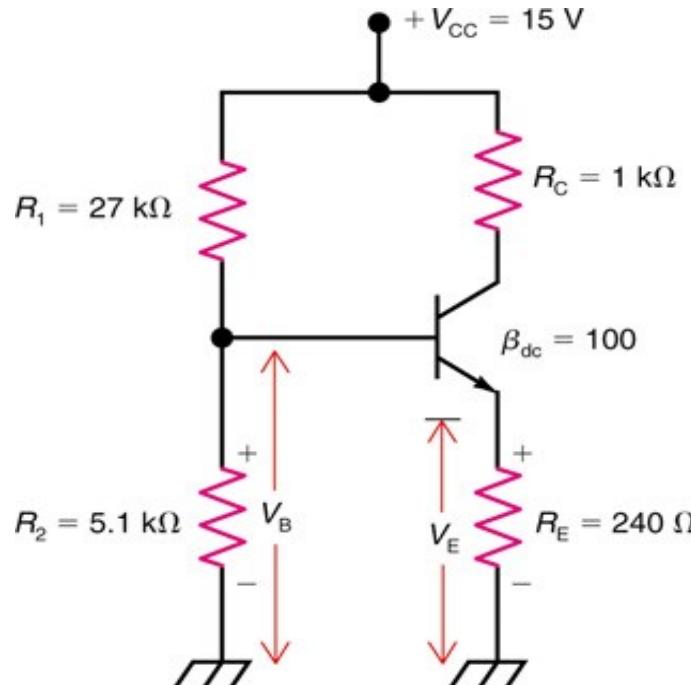
$$I_E \approx I_C$$



# Voltage Divider Bias – Example

---

- Solve for  $V_B$ ,  $V_E$ ,  $I_E$ ,  $I_C$ ,  $V_C$  and  $V_{CE}$
- Construct a dc load line showing the values of  $I_{C(sat)}$ ,  $V_{CE(off)}$ ,  $I_{CQ}$  and  $V_{CEQ}$



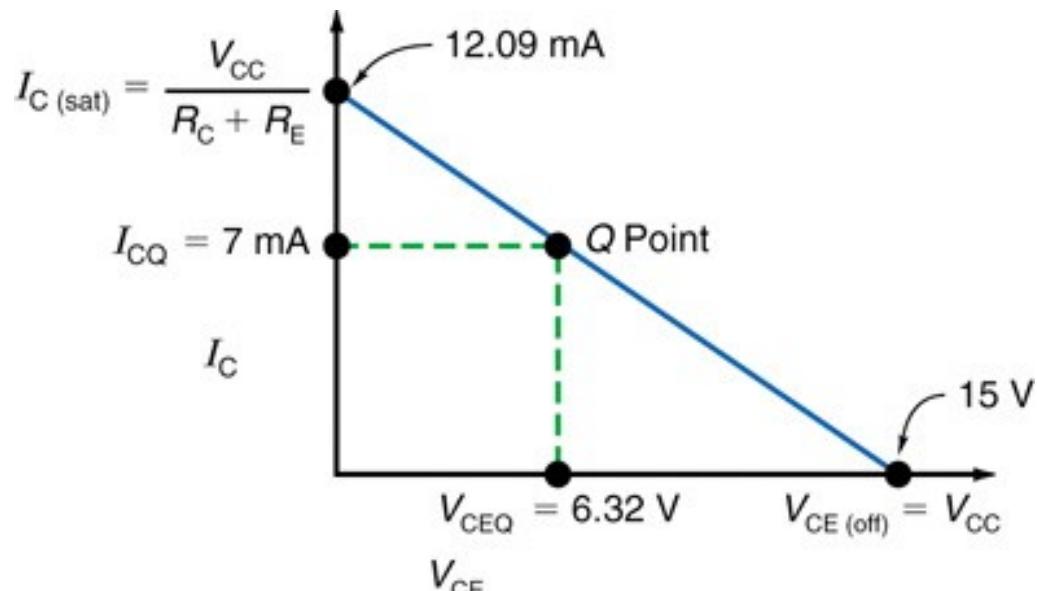
# Transistor Biasing

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- Fig. shows the **dc load line** for voltage-divider biased transistor circuit in previous slide

- End points and Q points are

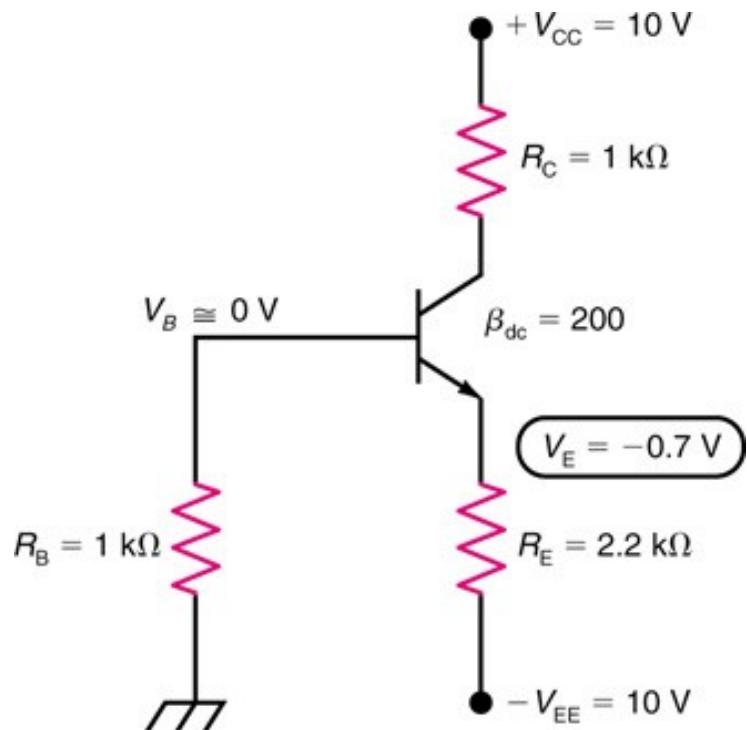
- $I_C (\text{sat}) = 12.09 \text{ mA}$
- $V_{CE} (\text{off}) = 15 \text{ V}$
- $I_{CQ} = 7 \text{ mA}$
- $V_{CEQ} = 6.32 \text{ V}$



# Transistor Biasing

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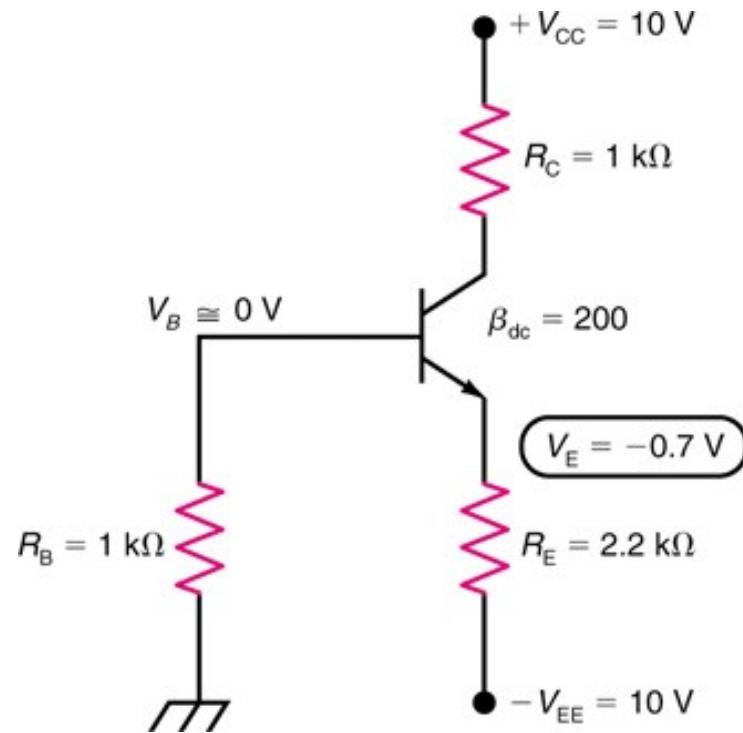
- Both positive and negative power supplies are available
- **Emitter bias** provides a solid Q point that fluctuates very little with temperature variation and transistor replacement.



# Emitter Bias - Example

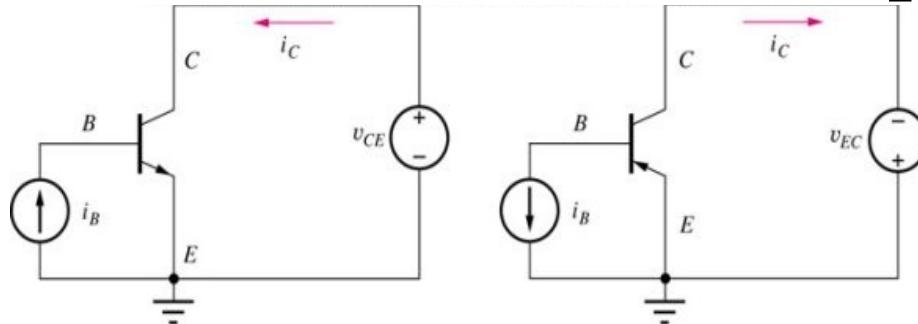
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- Solve for  $I_E$ , and  $V_C$



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# $i$ - $v$ Characteristics Bipolar Transistor: Common-Emitter Output Characteristics

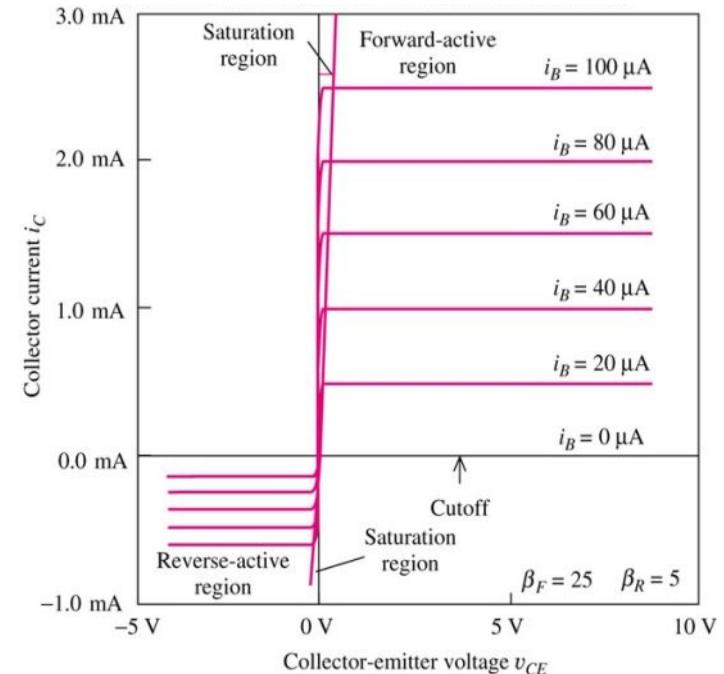


For  $i_B = 0$ , the transistor is cutoff. If  $i_B > 0$ ,  $i_C$  also increases.

For  $v_{CE} > v_{BE}$ , the *npn* transistor is in the forward active region,  $i_C = \beta_F i_B$  is independent of  $v_{CE}$ .

For  $v_{CE} < v_{BE}$ , the transistor is in saturation.

For  $v_{CE} < 0$ , the roles of collector and emitter are reversed.



# Transistor Ratings

- A transistor, like any other device, has limitations on its operations.
- These limitations are specified in the manufacturer's data sheet.
- Maximum ratings are given for
  - Collector-base voltage
  - Collector-emitter voltage
  - Emitter-base voltage
  - Collector current
  - Power dissipation

# Junction Breakdown Voltages

- If reverse voltage across either of the two *pn* junctions in the transistor is too large, the corresponding diode will break down.
- The emitter is the most heavily doped region, and the collector is the most lightly doped region.
- Due to these doping differences, the base-emitter diode has a relatively low breakdown voltage (3 to 10 V). The collector-base diode is typically designed to break down at much larger voltages.
- Transistors must therefore be selected in accordance with the possible reverse voltages in circuit.